

# Neutrons in Radiotherapy: Semiconductor Dosimetry

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# Summary

Principle of Semiconductor Neutron Dosimetry in:

- ▶ Fast Neutron Therapy
- ▶ Boron Neutron Capture Therapy
- ▶ Proton Therapy
- ▶ Medical X-ray LINAC



# Physics of Neutron Therapy

- ▶ Indirectly ionizing
- ▶ Sets in motion protons and heavy recoils

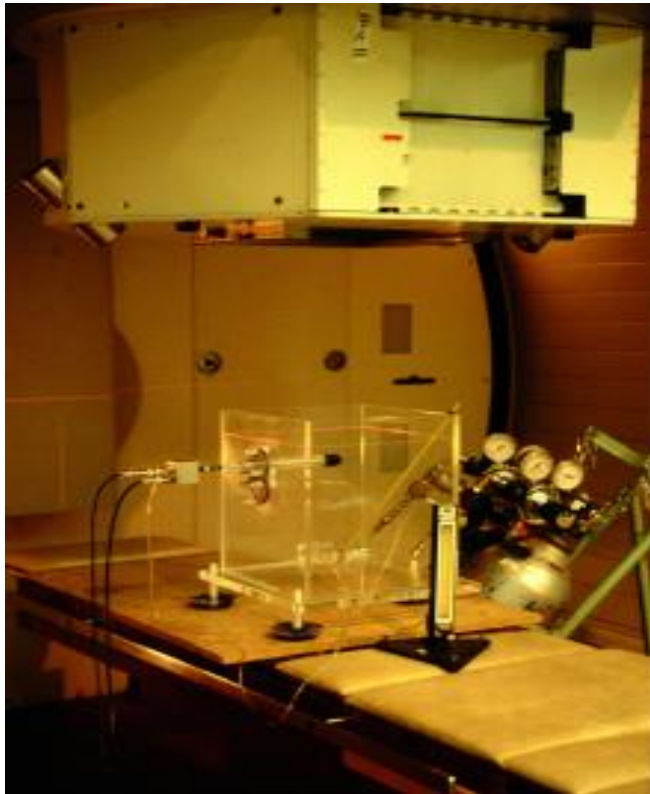
Elastic:  $n + X \rightarrow n + X$

Inelastic:  $n + X \rightarrow C^* + b + Y$   
 $(n,n) (n,p) (n,d) (n,\alpha) (n,\gamma) (n,X)$

- ▶ Neutrons deposit 20-100 times more energy per unit length than x-rays (LET: 100eV/ $\mu$ )
- ▶ Neutrons always accompanied by gamma radiation:

$$D_{\text{Total}} = D_{\text{neutron}} + D_{\gamma}$$

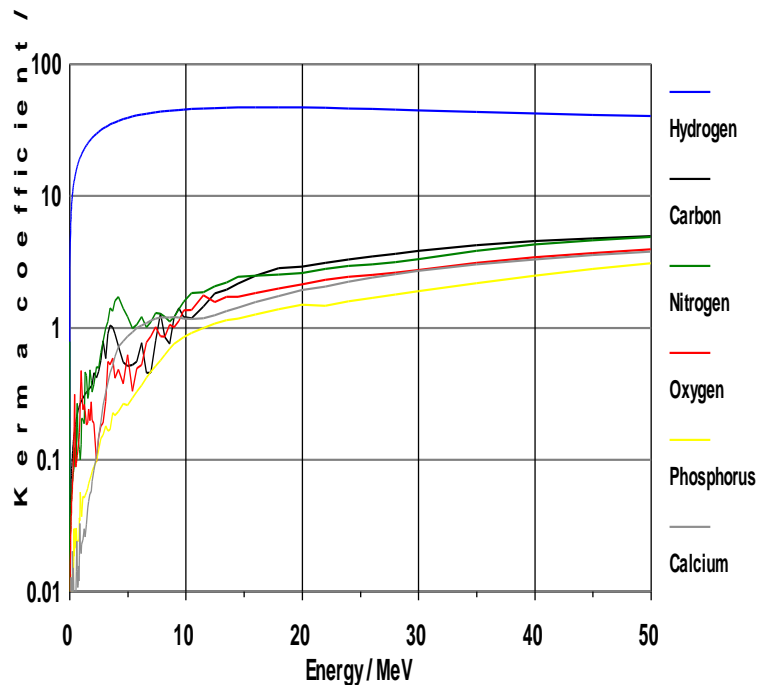
# Physics of Neutron Therapy



- ▶ Total dose can be measured with ion chambers based on Bragg-Gray relationship:

$$D_T = \frac{Q_n}{m} \cdot \frac{W_n}{e} \cdot (r_{m,g})_n \cdot \left( \frac{K_t}{K_m} \right) \cdot d_T \cdot \frac{1}{1+\delta}$$

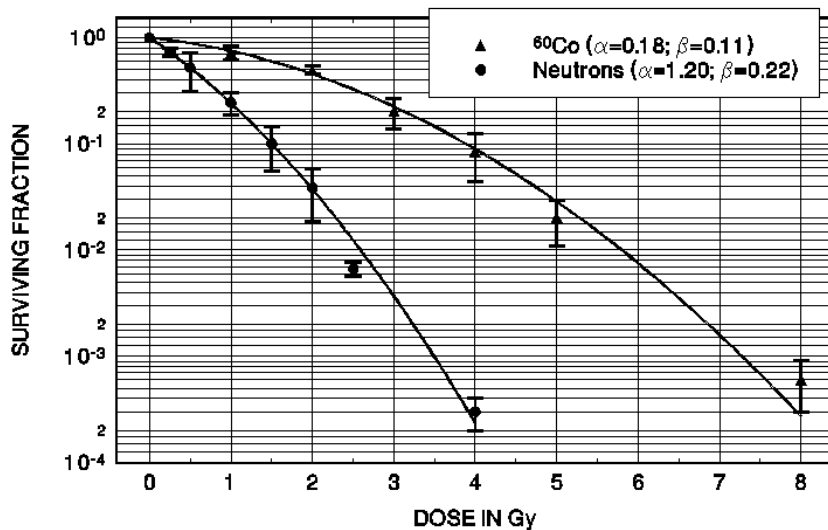
# Physics of Neutron Therapy



- ▶ Effect of tissue elemental composition on neutron dosimetry

Tissue	Kerma
Muscle	5.85 fGy·m <sup>2</sup>
Inner Bone	5.28 “
Cortical Bone	3.05 “
Adipose	6.57 “
Lung	5.88 “

# Radiobiology of Neutron Therapy



- ▶ Steep survival curves
- ▶ Low OER
- ▶ Less variability in radiosensitivity across the cell cycle

# Radiobiology of Neutron Therapy

- ▶ Less repair of sublethal and potentially lethal damage
- ▶ Hypoxic and slowly growing tumors
- ▶ Increased RBE
  - RBE=4 for cancer
  - RBE=3 for normal tissue

# Harper Hospital Superconducting Cyclotron: Operational Parameters

- ▶ Liquid He: 100 liters
- ▶ Magnetic Field: from 4.6T to 5.4T
- ▶ RF: 105 MHz from 25kW transmitter
- ▶ Magnet Current: 203 A
- ▶ Ion Source: deuterium discharge (2.8 kV, 350mA)
- ▶ Target: Be (15.9 x 20.1 x 3.2 mm), 20.3°
- ▶ Beam Current: 15  $\mu$ A
- ▶ Neutron Production:  $d(48.5)+Be$

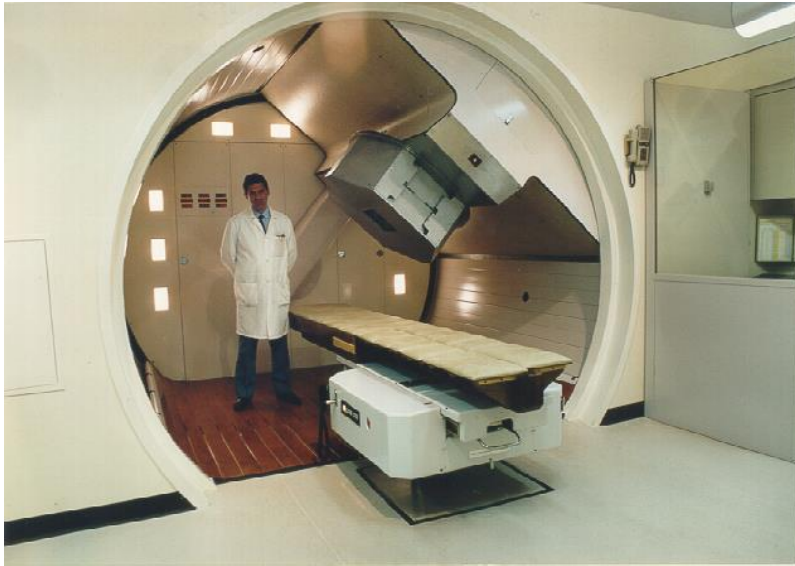


# Harper Hospital Superconducting Cyclotron: Operational Parameters



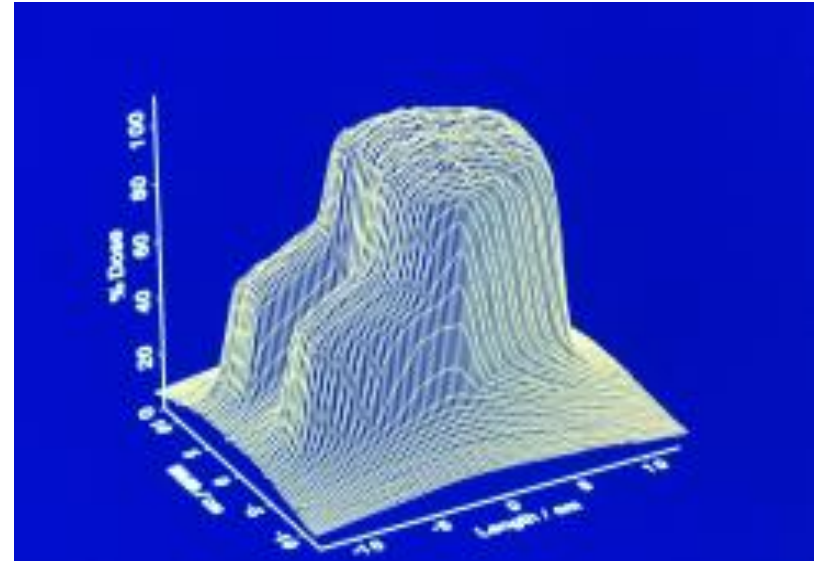
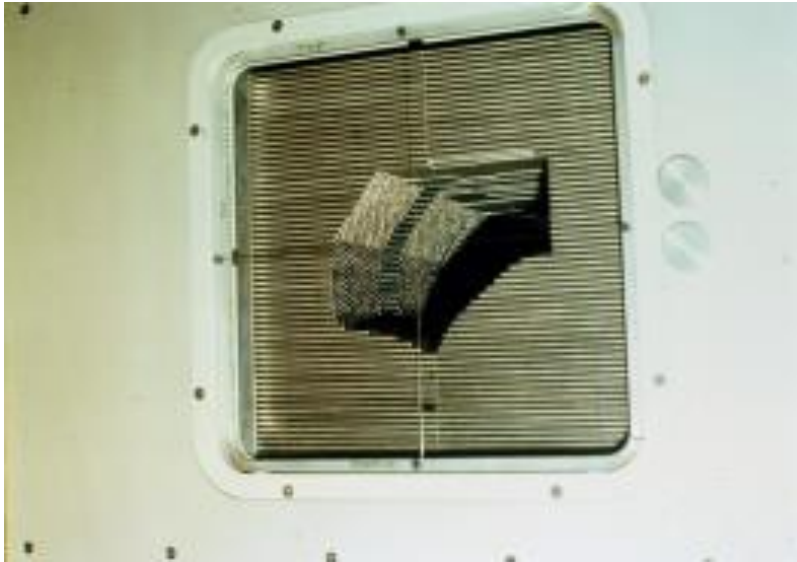
- ▶ Cyclotron: 25 T
- ▶ Beam Stop: 25 T
- ▶ Mounted on two concentric rings
- ▶ Full 360° rotation
- ▶ Isocenter: 1829 mm
- ▶ Output:  $3.2 \text{ cGy}\cdot\text{min}^{-1}\cdot\mu\text{A}^{-1}$

# Harper Hospital Superconducting Cyclotron: Installation

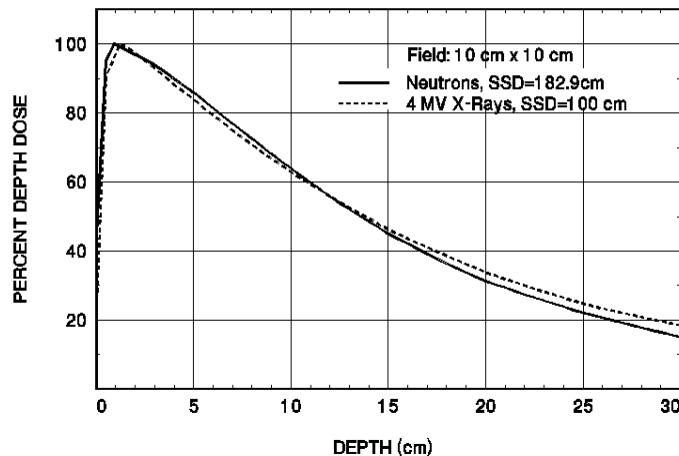


- ▶ 1990 - Under direction of Prof . Richard. L. Maughan
- ▶ Sept. 1991: First patient treated
- ▶ March 1992: Clinical trials

# Multi-Rod Collimator



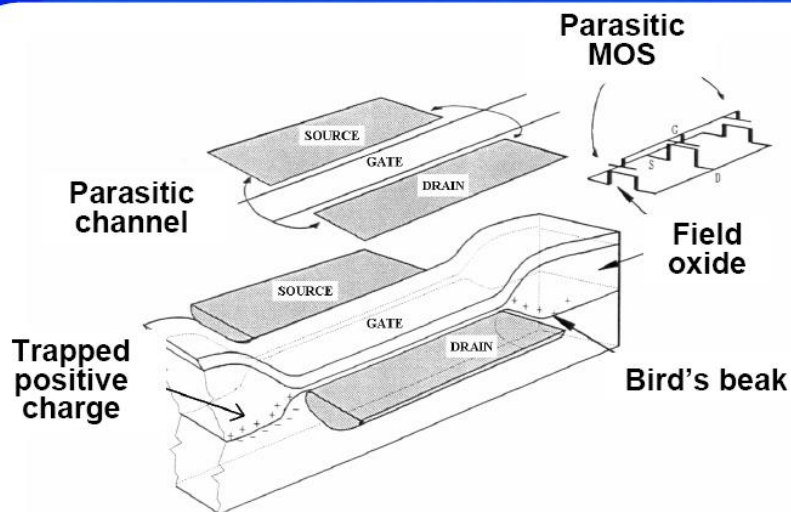
# Neutron Beam Physical Characteristics: Depth Dose



- ▶ Resembles 4 MV Photons
- ▶  $d_{\max} = 0.9$  cm in tissue
- ▶  $d_{50\%} = 13.6$  cm
- ▶  $D_{\text{surface}} = 42\%$
- ▶ Penumbra (20%-80%):
  - 0.60 cm @  $d_{\max}$
  - 1.90 cm @ 10 cm depth
  - 3.40 cm @ 20 cm depth

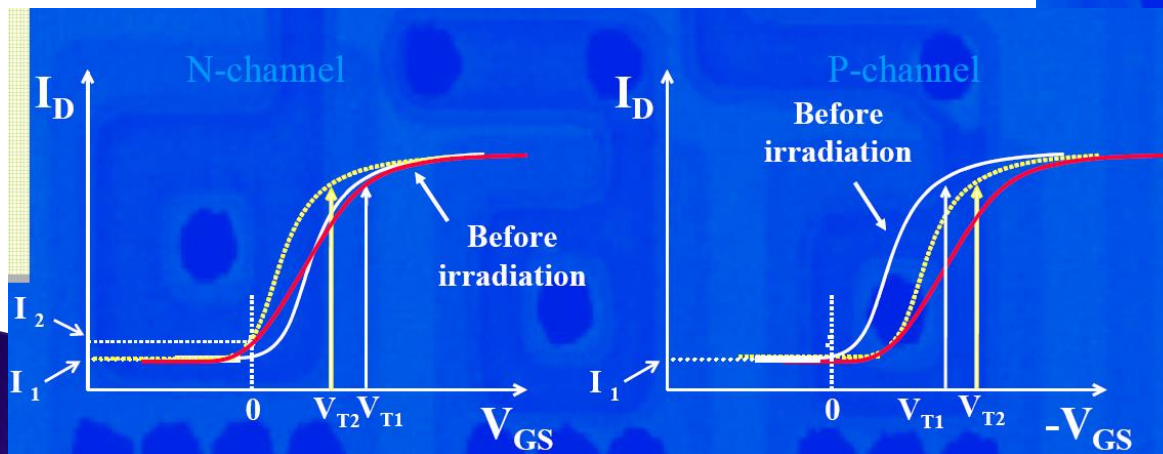
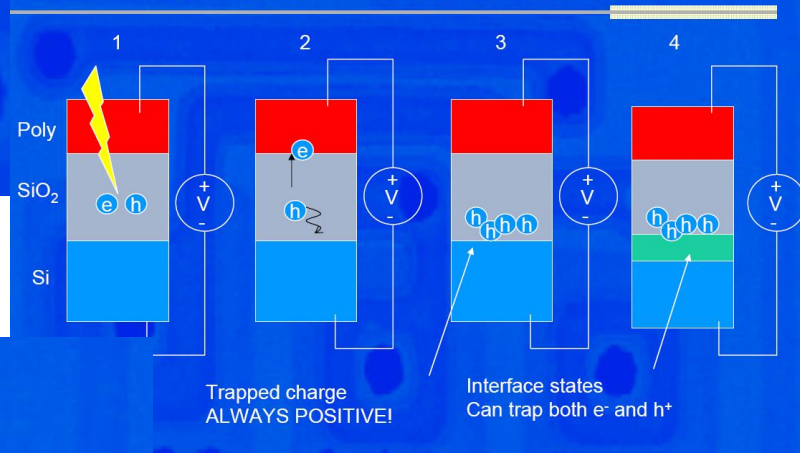
# TOTAL DOSE EFFECTS on MOSFETs:

## Voltage threshold shifting



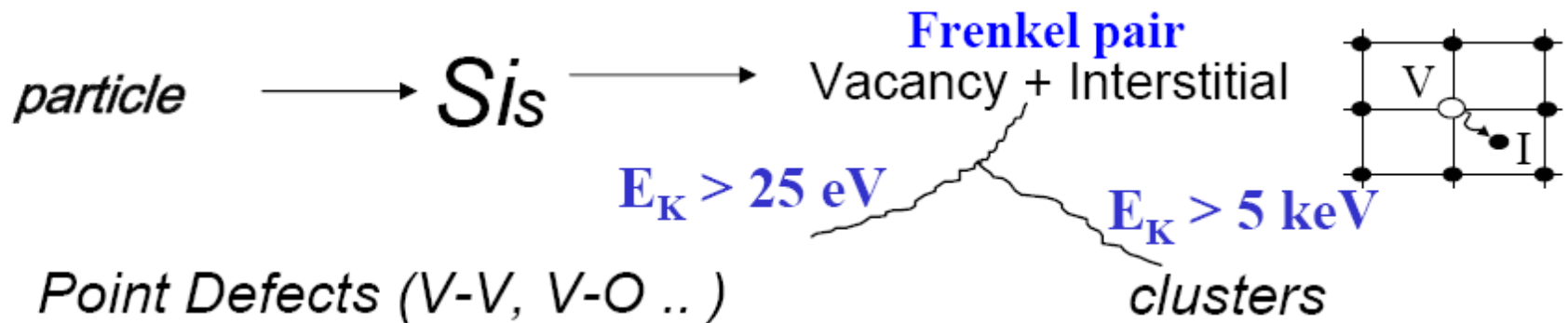
~~Source~~  
~~Drain~~

### TID in MOS structures



# Radiation damage in silicon detectors: The microscopic point of view

- ▶ Radiation induced lattice defects:
  - Traps
  - Generation and recombination centers
  - Clusters

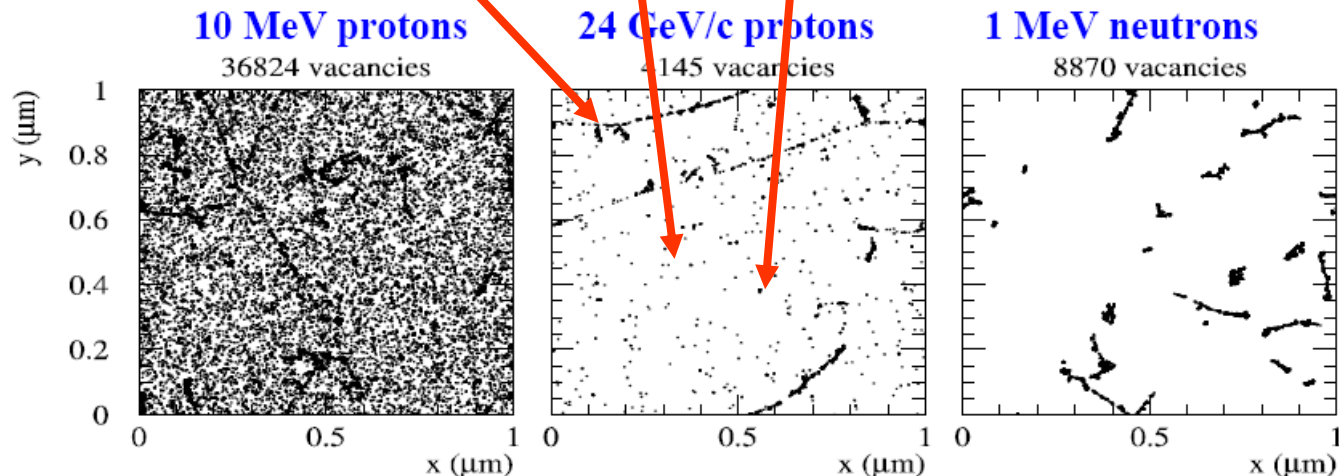


# The microscopic point of view

Vacancy amount and distribution depends on particle kind and energy.

- ▶  $^{60}\text{Co}$  – gammas: Compton electrons  $\rightarrow$  trapped charge (TID)
- ▶ Electrons:
  - low energy  $\rightarrow$  displacement
  - High energy  $\rightarrow$  clusters
- ▶ Neutrons:
  - Thermal  $\rightarrow$  displacement
  - Fast  $\rightarrow$  clusters

Initial distribution of vacancies in  $(1\mu\text{m})^3$  after  $10^{14}$  particles/cm<sup>2</sup>



# The microscopic point of view

## Primary Damage and secondary defect formation

- Two basic defects

I - Silicon Interstitial      V - Vacancy

- Primary defect generation

I, I<sub>2</sub>    higher order I (?)  
 ⇒ I - CLUSTER    (?) ←

V, V<sub>2</sub>,    higher order V (?)      Damage?!  
 ⇒ V - CLUSTER    (?) ←

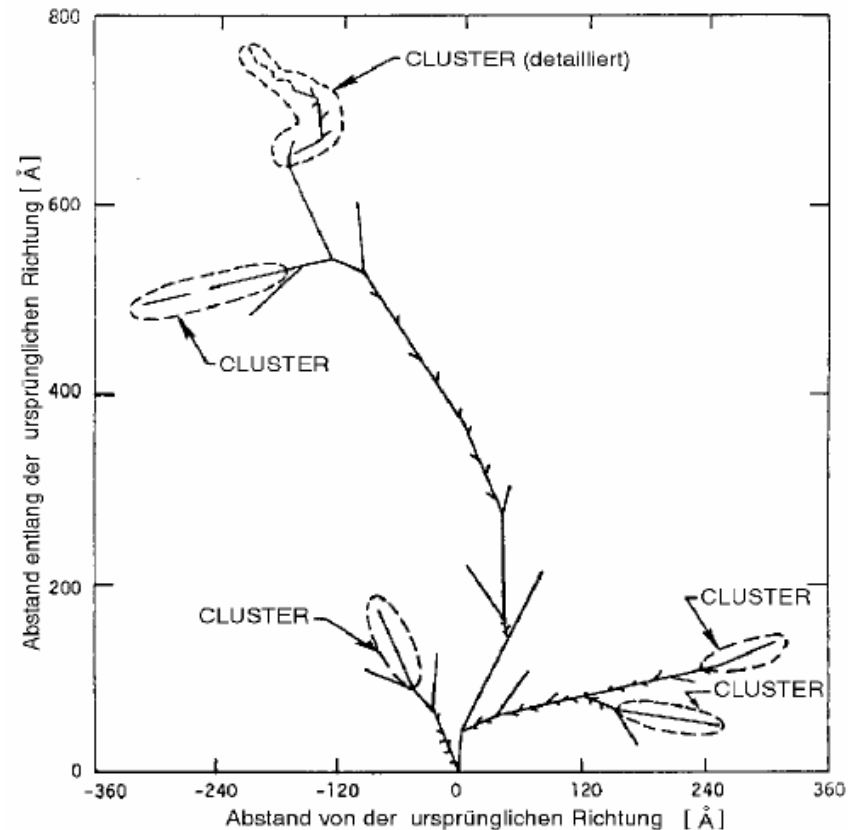
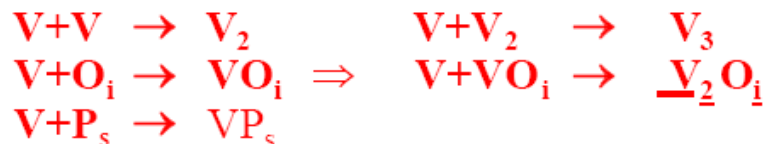
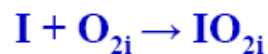
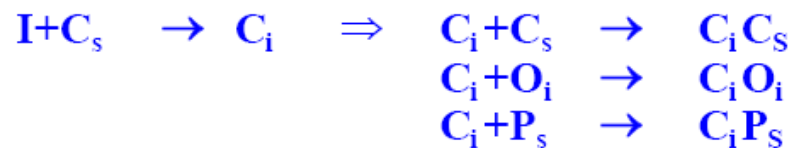
- Secondary defect generation

Dopants : P, B

Main impurities in silicon: Carbon C<sub>s</sub>

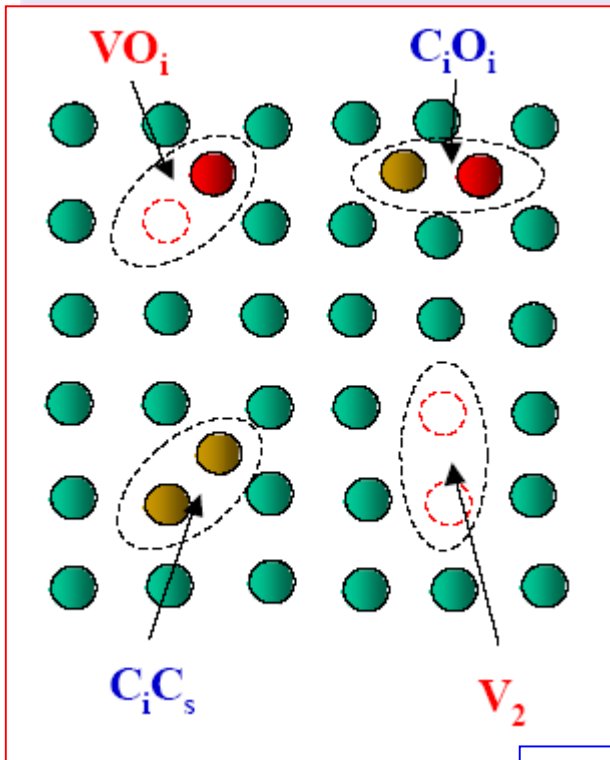
Oxygen O<sub>i</sub>

Oxygen dimer: O<sub>2i</sub>





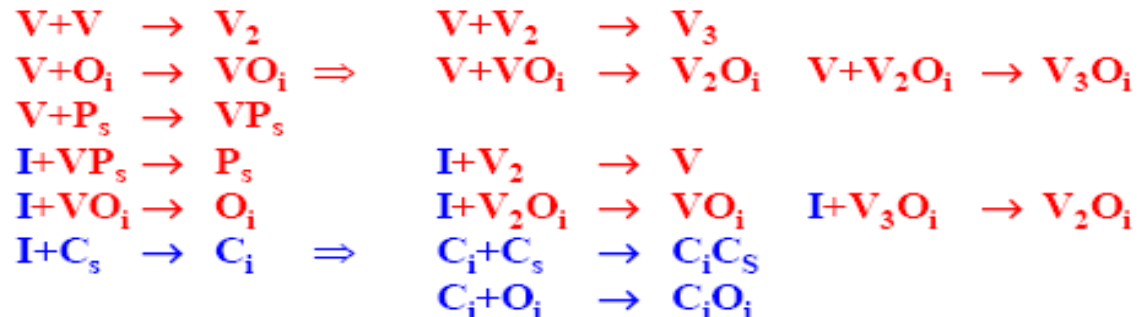
# The microscopic point of view



**Quasi-chemistry**  
with complex kinetics  
(time, concentration,  
temperature dependences)

O = Oxygen  
C = Carbon  
P = Phosphorus  
I = interstitial  
S = substitutive  
V = vacancy

## Various quasi-chemical reactions



# The microscopic point of view

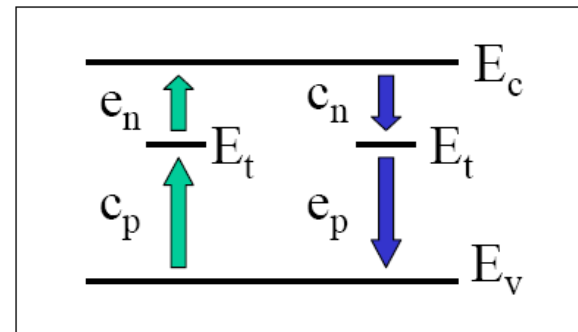
- ▶ Energy Levels related to traps: **main parameters**
  - $E_t$ : Activation energy
  - $\sigma$ : Cross section
  - $N_t$ : Concentration

Emission coefficient:

$$e_n = N_c \sigma_n v_{th} \cdot e^{-\frac{E_c - E_t}{KT}}$$

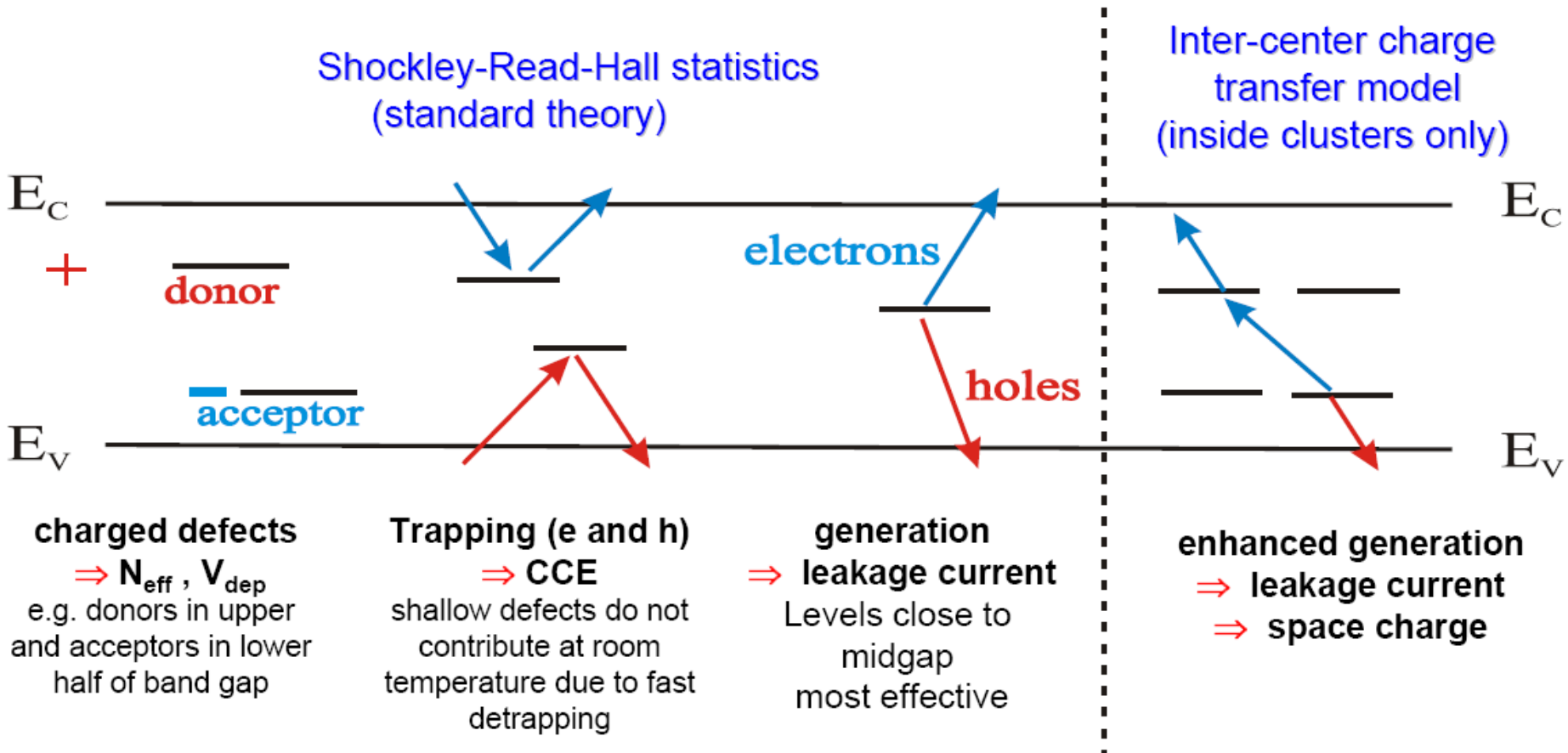
Capture coefficient :

$$c_n = n \sigma_n v_{th}$$



# From microscopic to MACROSCOPIC point of view

## Impact of Defects on Detector properties



Impact on detector properties can be calculated if all defect parameters are known:

$\sigma_{n,p}$  : cross sections

$\Delta E$  : ionization energy

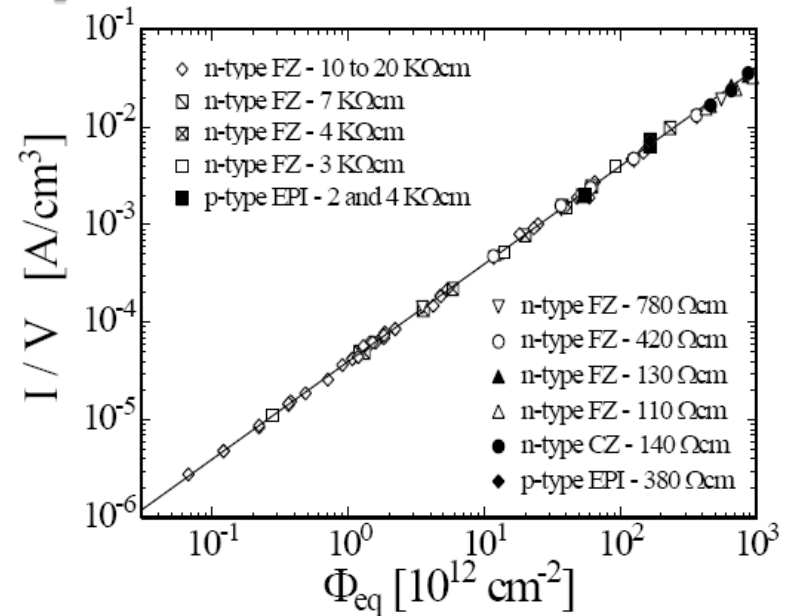
$N_t$  : concentration

# The MACROSCOPIC point of view

- Leakage current:

$$\frac{I_{dep}}{Volume} = \alpha \cdot \Phi$$

$$\alpha = 4 \cdot 10^{-17} \text{ A/cm}^3$$

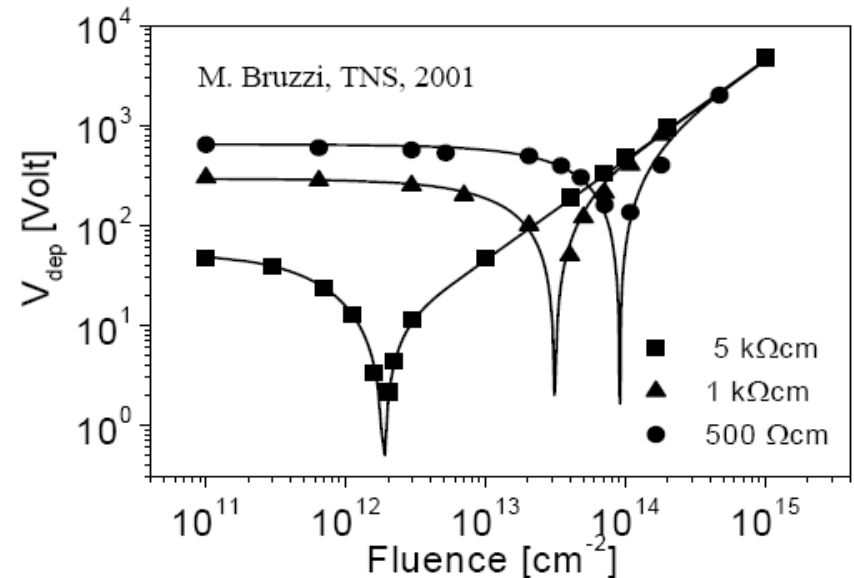


- Variation of doping concentration:

$$\Delta N_{eff}(\Phi) = | N_{c0}(1 - e^{-c\Phi}) - \beta \cdot \Phi |$$

Compensation of shallow doping concentration

Acceptor defects production



# The MACROSCOPIC point of view

- Decreasing of Charge Collection Efficiency (CCE):

$$Q = Q_0 \cdot \varepsilon_{\text{dep}} \cdot \varepsilon_{\text{trap}}$$

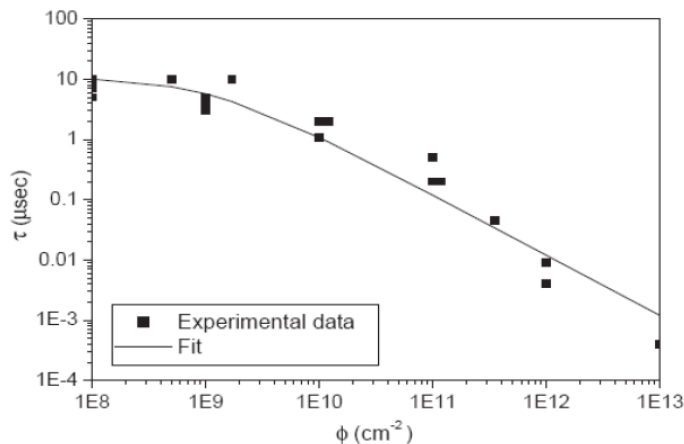
Where  $Q$ =collected charge

$Q_0$ =pre-irradiation collected charge

$\varepsilon_{\text{dep}}$ = sensitive volume “efficiency”

$\varepsilon_{\text{trap}}$ = collection time “efficiency”

$$\varepsilon_{\text{dep}} = \frac{W_0}{W_D} \quad \varepsilon_{\text{trap}} = e^{-\frac{\tau_c}{\tau_t}} \quad W_D = W_0 + L = \sqrt{\frac{2\varepsilon \cdot V_{bi}}{q \cdot N_{\text{eff}}}} + \sqrt{D_h \cdot \tau_h}$$



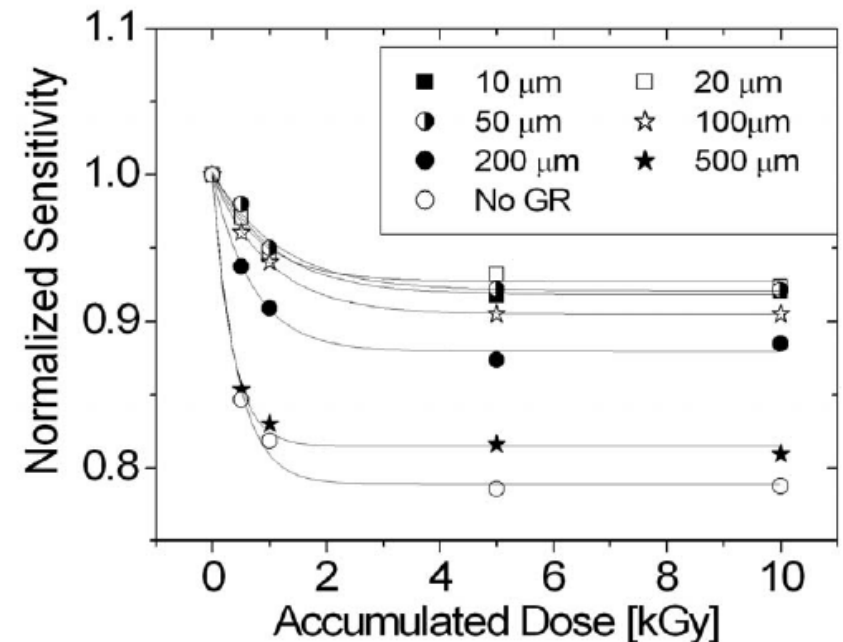
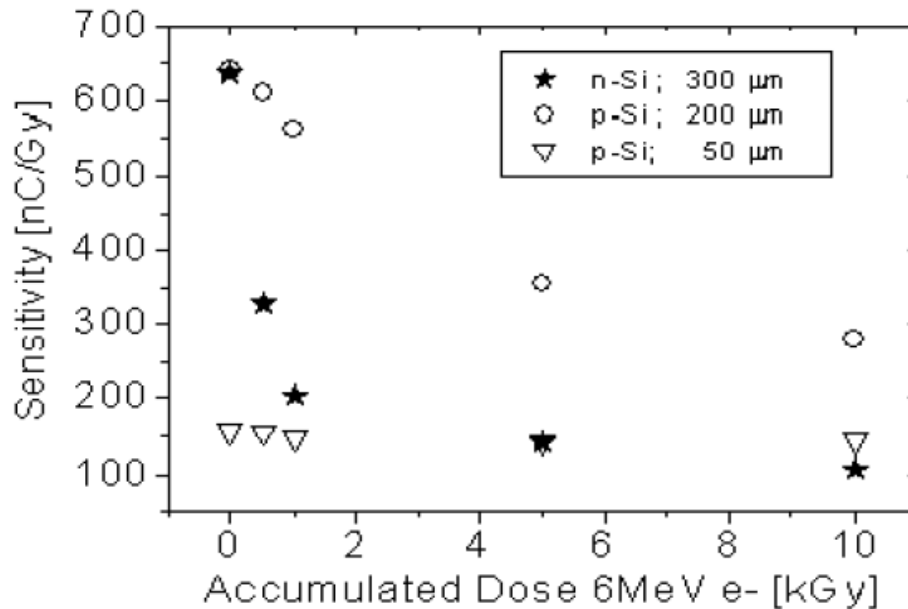
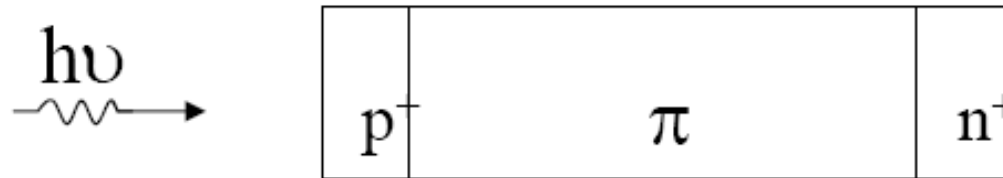
$$\frac{1}{\tau} = \frac{1}{\tau_0} + k_{\tau} \phi,$$

Per protoni da 10MeV

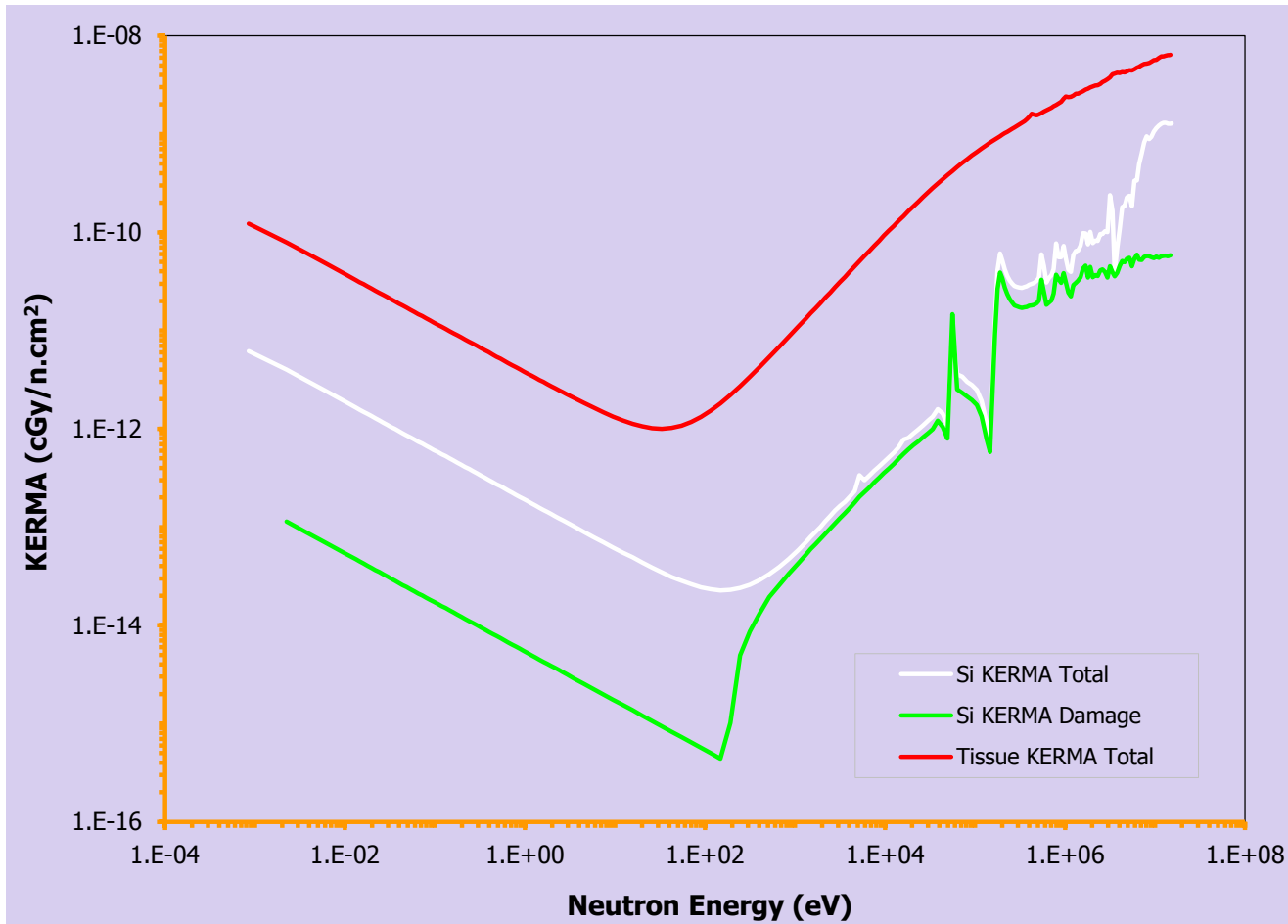
$$k_{\tau} = (1.52 \pm 0.05) \times 10^{-11} \mu\text{s}^{-1} \text{cm}^2$$

# The MACROSCOPIC point of view

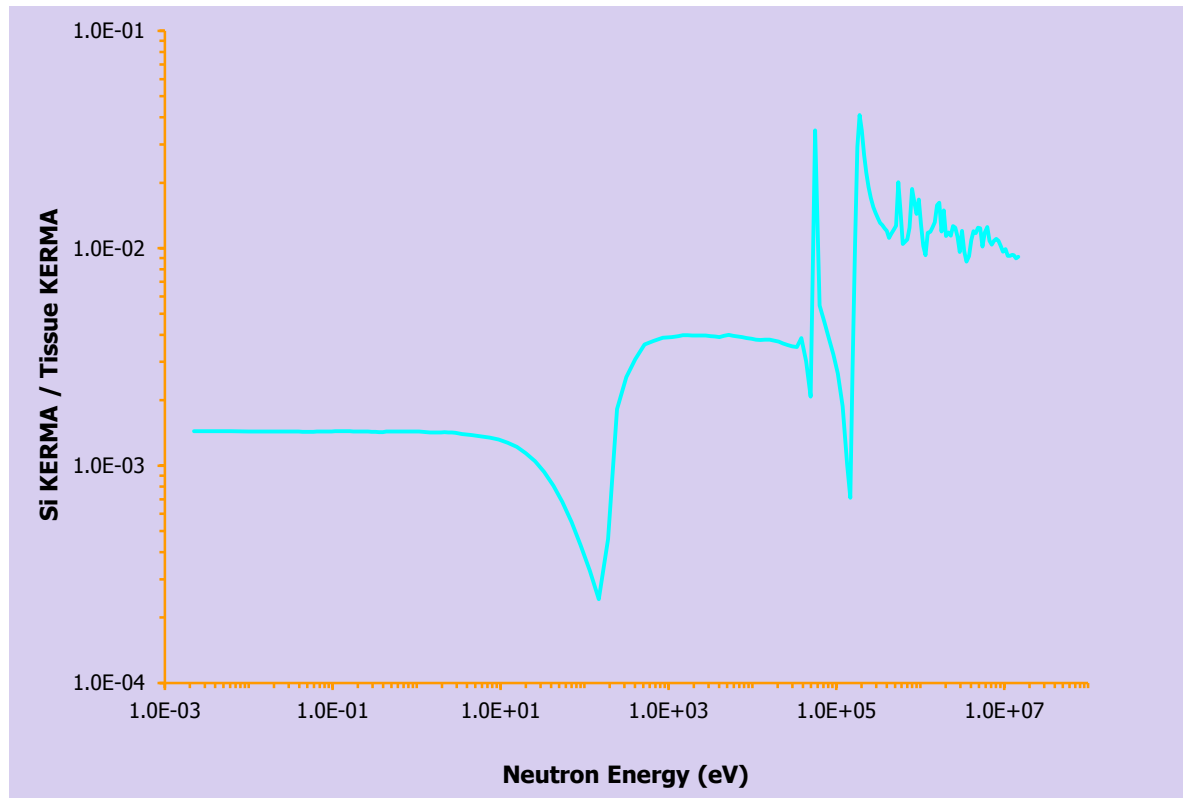
Dosimeters for radiation therapy – from 1983 to 2010!!



# Tissue and Silicon Neutron Kerma



# Ratio of Si Displacement Kerma to Tissue Kerma for Neutrons

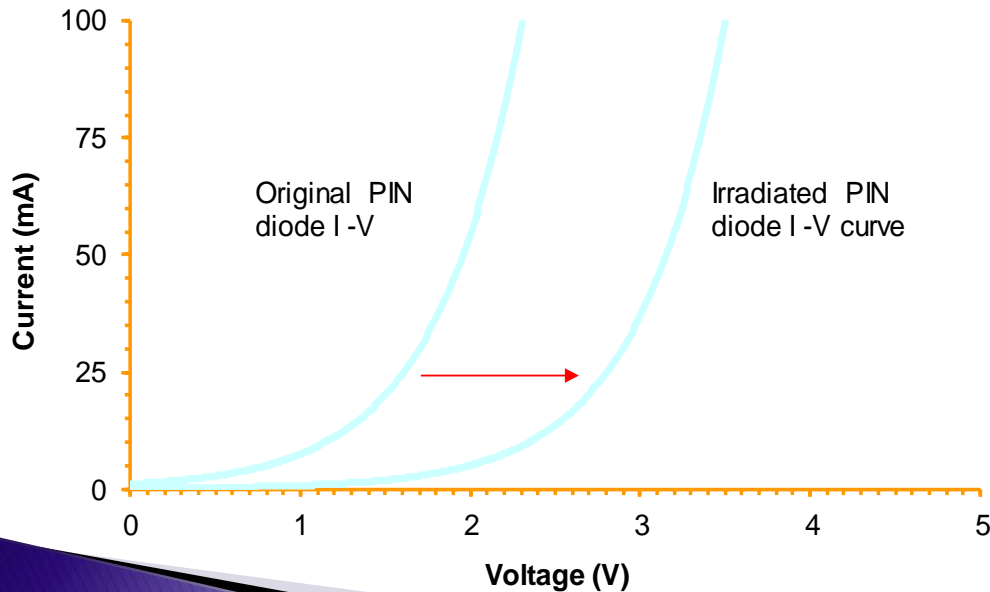
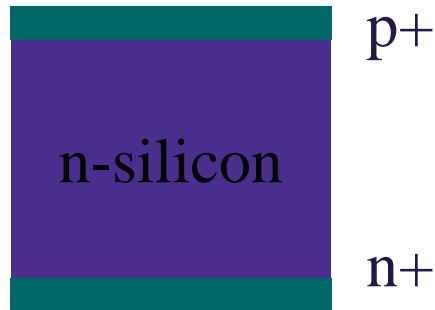


The ratio of Si displacement KERMA to tissue KERMA over some energy intervals is almost energy independent



# Method of neutron dosimetry

- ▶ The operation of the *p-i-n* diode neutron sensor is based on the change of forward voltage



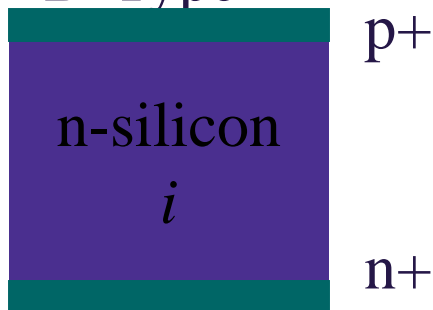
$$\frac{1}{\tau} - \frac{1}{\tau_0} = k_{\tau} \Phi$$

Sensitivity  $= \alpha W^2$   
W-diode base length

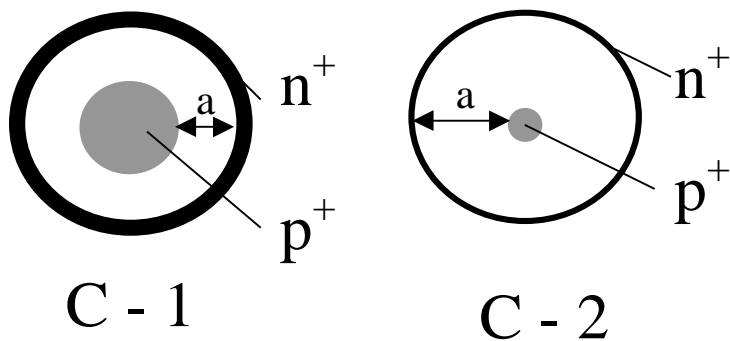
# Bulk and Planar Neutron Diodes

Neutron detectors based on radiation damage

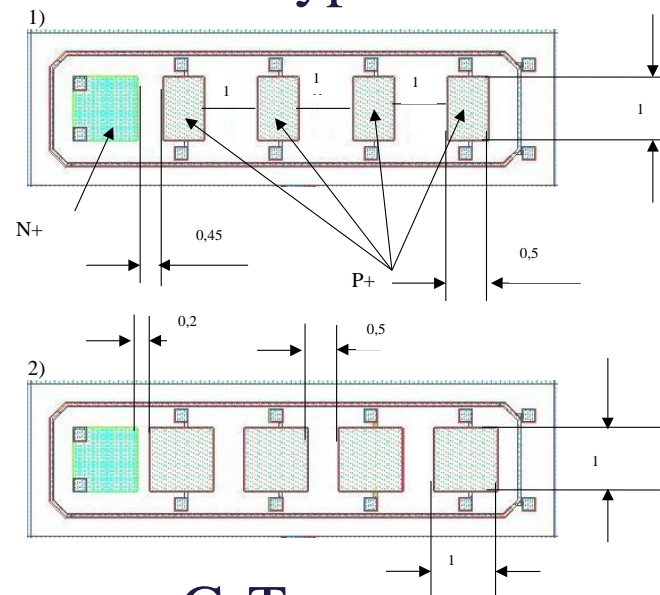
D-Type



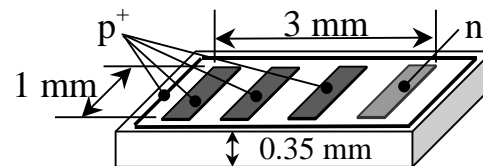
C-Type



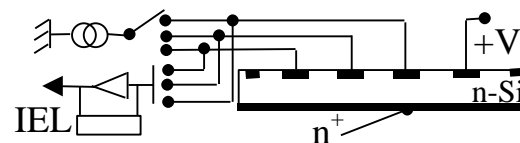
L-Type



G-Type

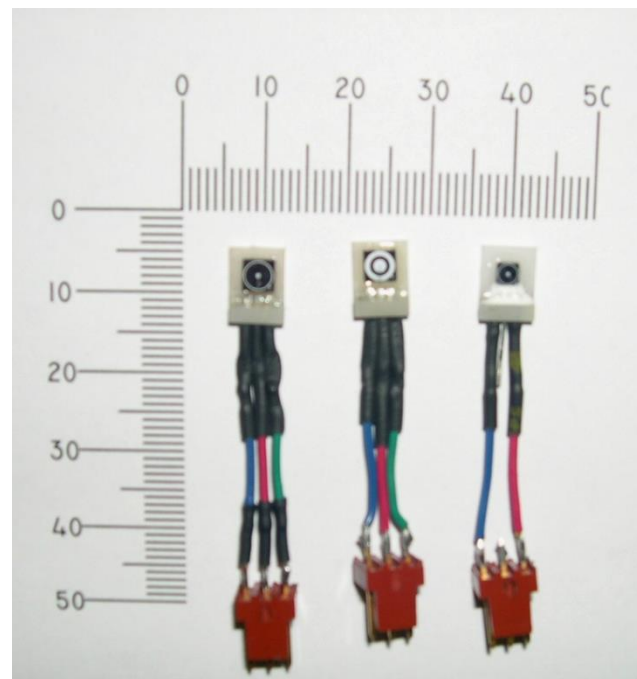


Passive sensor: based on forward voltage change after irradiation



# Introduction

- ▶ New type of semiconductor dosimeters based on ion implanted miniature planar *p-i-n* diodes was developed
- ▶ Dosimeter combines two types:
  - Planar *p-i-n* diodes
  - Bulk *p-i-n* diodes
- ▶ The forward voltage drop across the *p-i-n* diode is proportional to neutron induced damage (NIEL) and correlates with neutron dose
- ▶ The current produced due to the secondary charged particle interactions (IEL) correlates with the total (neutron + gamma) dose



# Application for Neutron Dosimetry

- ▶ The response of the diode in mixed ( $D_n + D_\gamma$ ) beam:
  - Voltage drop mode:

$$R_{mV} = C_{n,mV} \cdot D_n$$

- Charge mode:

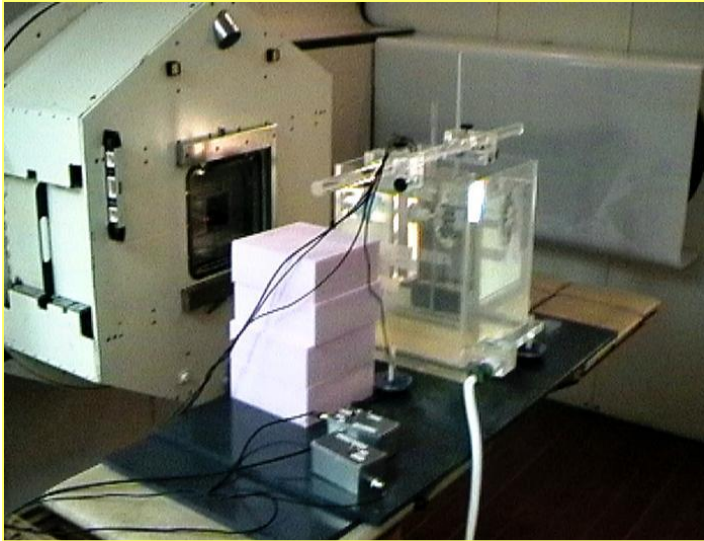
$$R_{nC} = C_{n,nC} \cdot D_n + C_\gamma \cdot D_\gamma$$

$C_{n,mV}$  is the sensitivity of the diode to neutrons in mV/cGy

$C_{n,nC}$  is the sensitivity of the diode to neutrons in nC/cGy

$C_\gamma$  is the sensitivity of the diode to gamma in nC/cGy

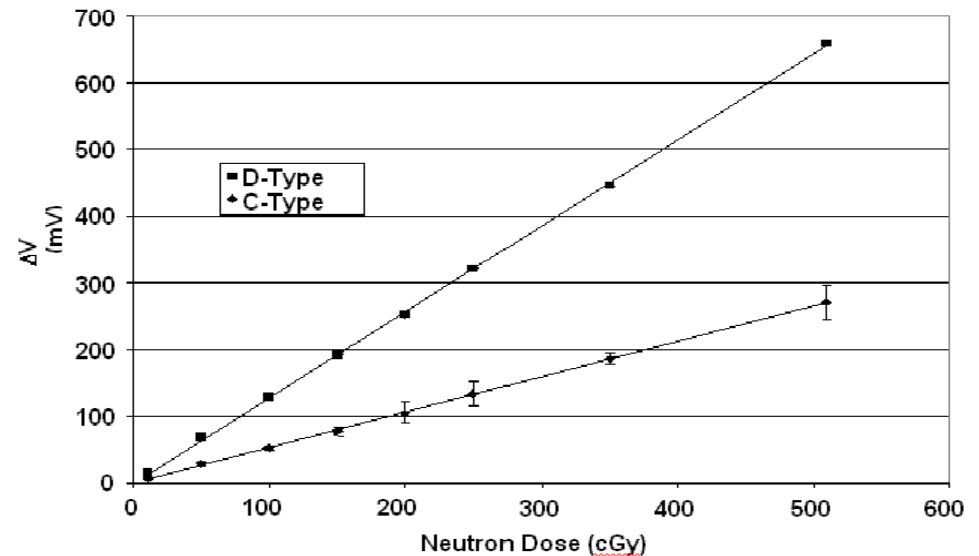
# Fast Neutron Therapy



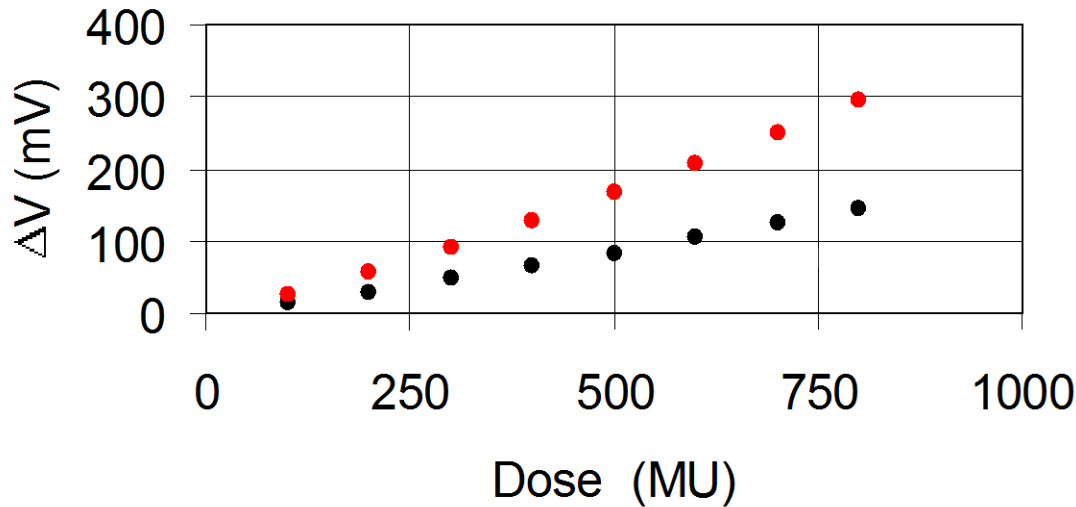
Two types of neutron *p-i-n* diodes were investigated –  
D type bulk Si sensor 1mm<sup>3</sup>  
C type planar circular shape

Gershenson Radiation Oncology  
Center, Harper Hospital, Detroit

Phantom depth 5cm in water,  
10 x 10 cm<sup>2</sup> beam, central axis

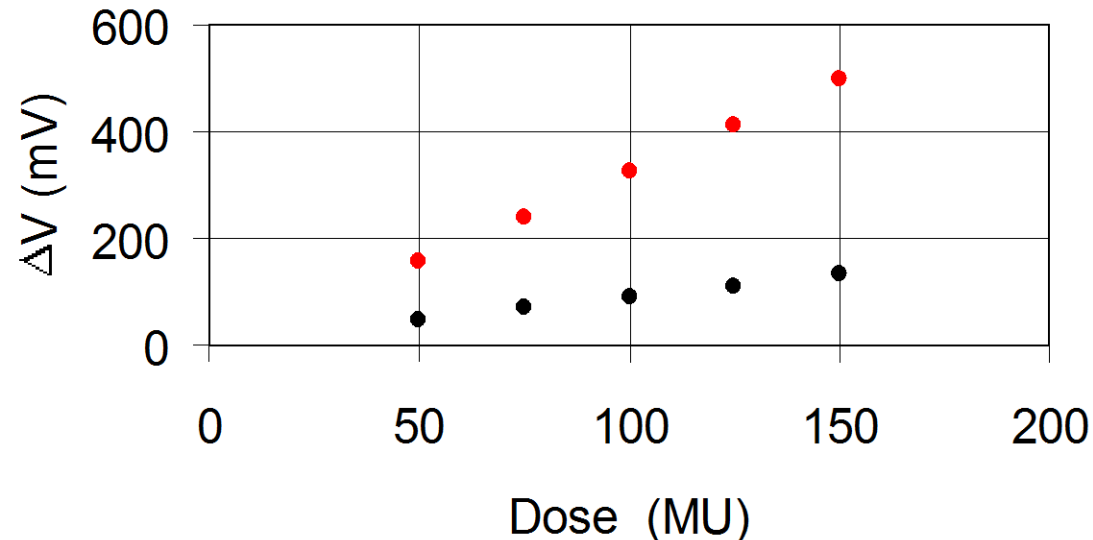


# Neutron response of C-Type *p-i-n* diodes

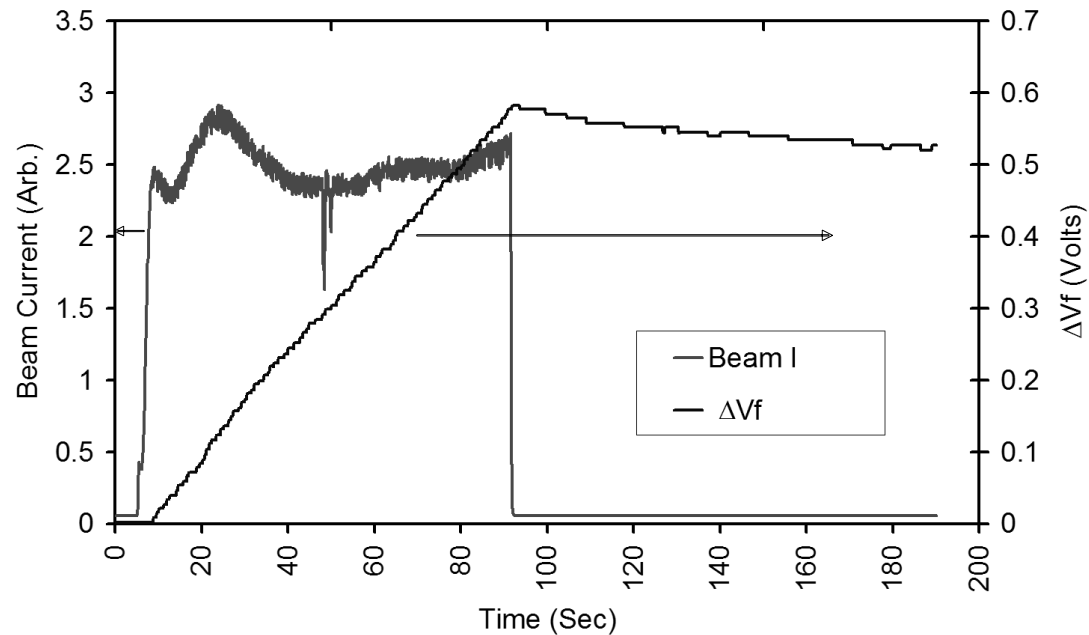


Neutron response of C-1 at depth 5 cm in a water for two readout currents 1 and 20 mA. The sensitivity is 0.14 mV/MU and 0.30mV/MU at point of irradiation.

Neutron response of C-2 at depth 5 cm in a water for two readout currents 1 and 20 mA. The sensitivity is 0.88 and 3.32 mV/MU for C-2 diode. 1 MU ~1cGy at point of irradiation



# Beam Target Current and P-I-N Diode Voltage Drop



Neutron Production:  $d(48.5)+Be$   
d-beam current about 15uA

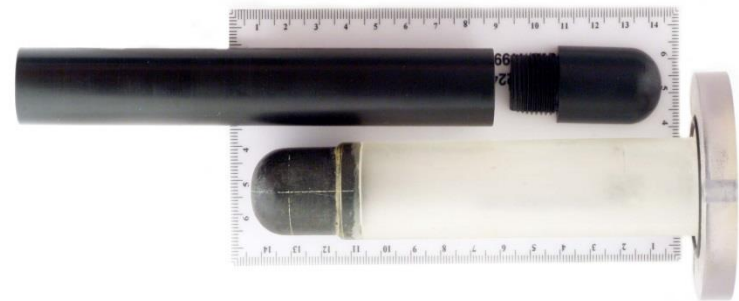
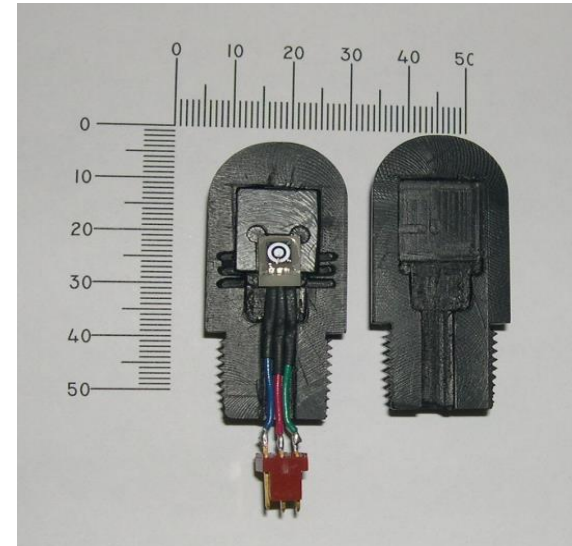
# Objectives

- ▶ Determine the neutron and the gamma sensitivity of the diode for each mode of operation
- ▶ Investigate various dosimetry applications of the diode in  $d(48.5)+Be$  beam
  - Lateral beam profile
  - Central axis depth dose
  - Opened and closed collimator
- ▶ Compare the results with conventional dosimetry methods

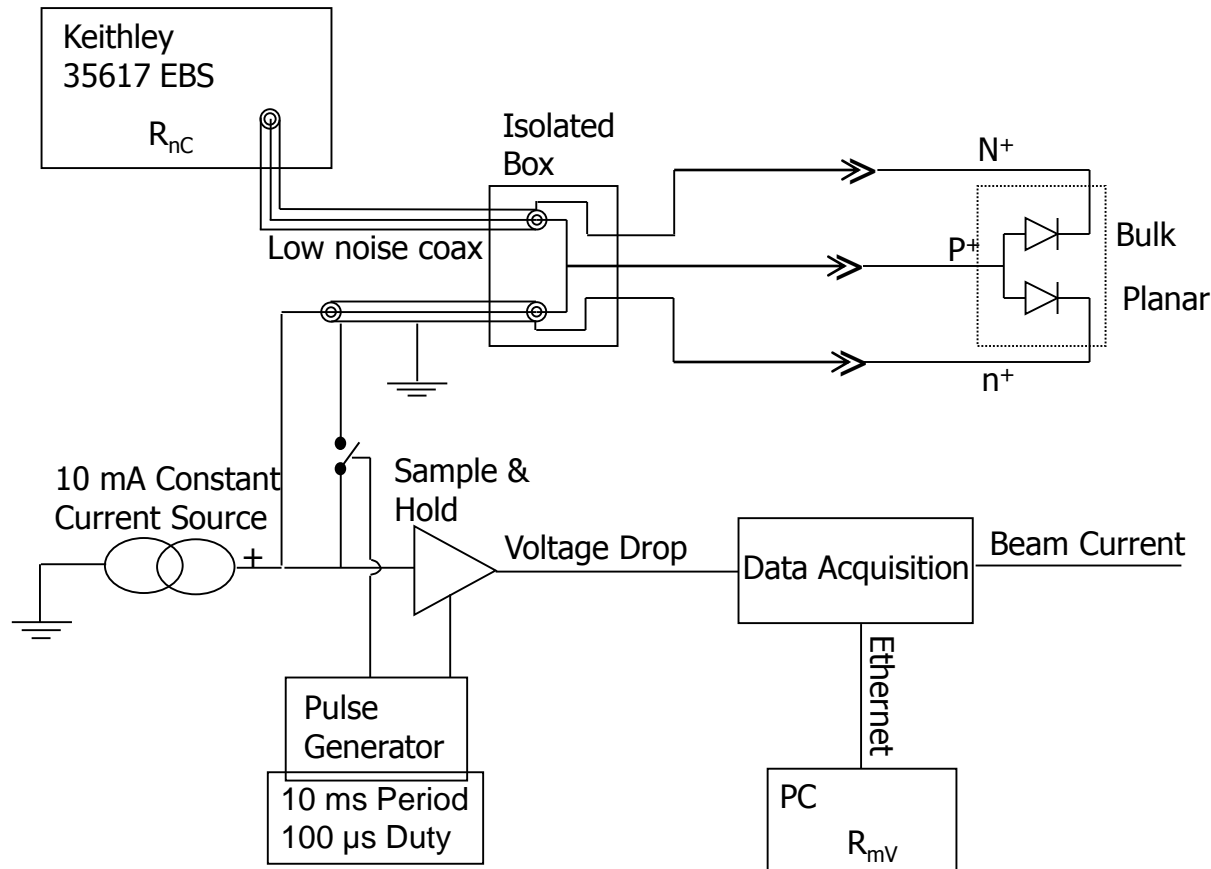


# Irradiation conditions

- ▶  $d(48.5)+Be$  beam from clinical superconducting cyclotron
- ▶ Diodes embedded in A150 TEP holder
- ▶ Measurements:
  - In  $5 \times 5 \text{ cm}^2$  field in air
  - Lateral dose profile at 5 cm depth in  $10 \times 10 \text{ cm}^2$  field in a water phantom
  - Depth dose along the central axis in  $10 \times 10$  and  $15 \times 15 \text{ cm}^2$  fields and  $30 \times 30 \text{ cm}^2$  field partially blocked with an equivalent of 93.5 mm of tungsten



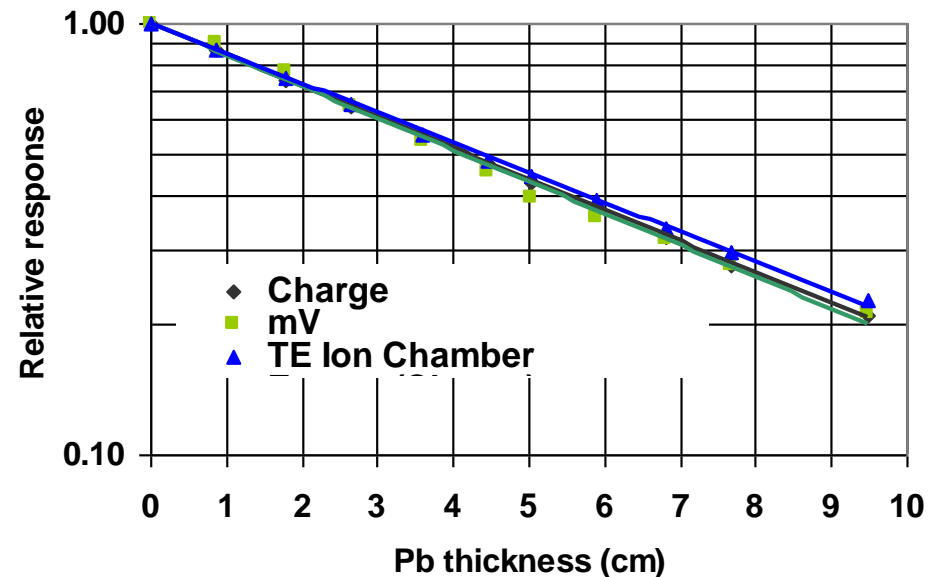
# Measurements in Twin Detector Mode: single sensor for simultaneous g-n dosimetry



# Neutron Sensitivity by Lead Attenuation Method

- ▶ The responses of the TE ionization chamber and the diode,  $R_{TE}$ ,  $R_{mV}$  and  $R_Q$ , are measured in narrow beam geometry as a function of lead absorber thickness
- ▶ The responses are related to the lead thickness,  $t$ , and gamma ray attenuation coefficient,  $\mu$ , as:

$$\bar{R} = \frac{R(t) - R(0) \cdot \exp(\mu \cdot t)}{1 - \exp(\mu \cdot t)}$$



# Neutron Sensitivity of the Diode Operated in the Voltage Drop Mode

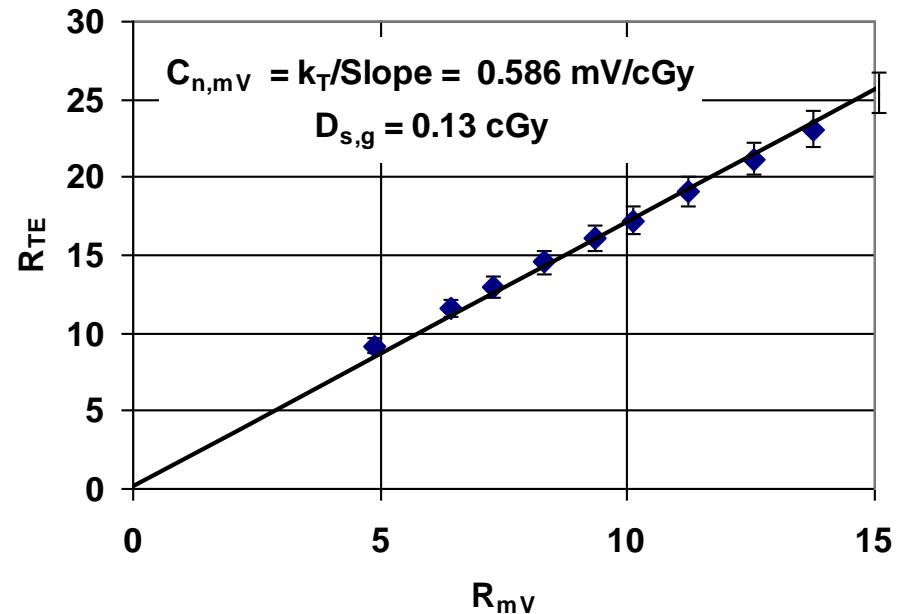
- ▶ Linear relationship between the modified responses of TE ionization chamber and the diode:

$$\bar{R}_{TE} = \frac{k_T}{C_{n,mV}} \cdot \bar{R}_{mV} + D_{s,\gamma}$$

$k_T$  is relative neutron sensitivity of TE ionization chamber

$$k_T = 0.994$$

$D_{s,\gamma}$  is the gamma dose due to the scatter arising from the shielding and surrounding



# Neutron Sensitivity of the Diode Operated in the Charge Collection Mode

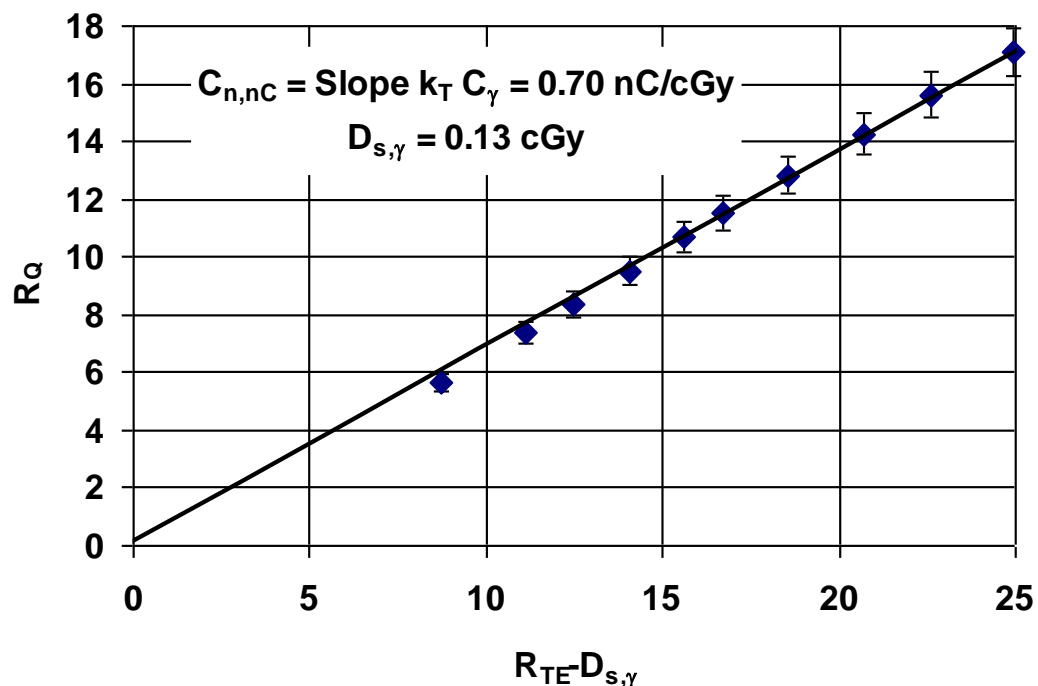
- ▶ Linear relationship between the modified responses of the diode and the TE ionization chamber is given by:

$$\bar{R}_Q = \frac{k_Q}{k_T} (\bar{R}_{TE} - D_{s,\gamma}) + D_{s,\gamma}$$

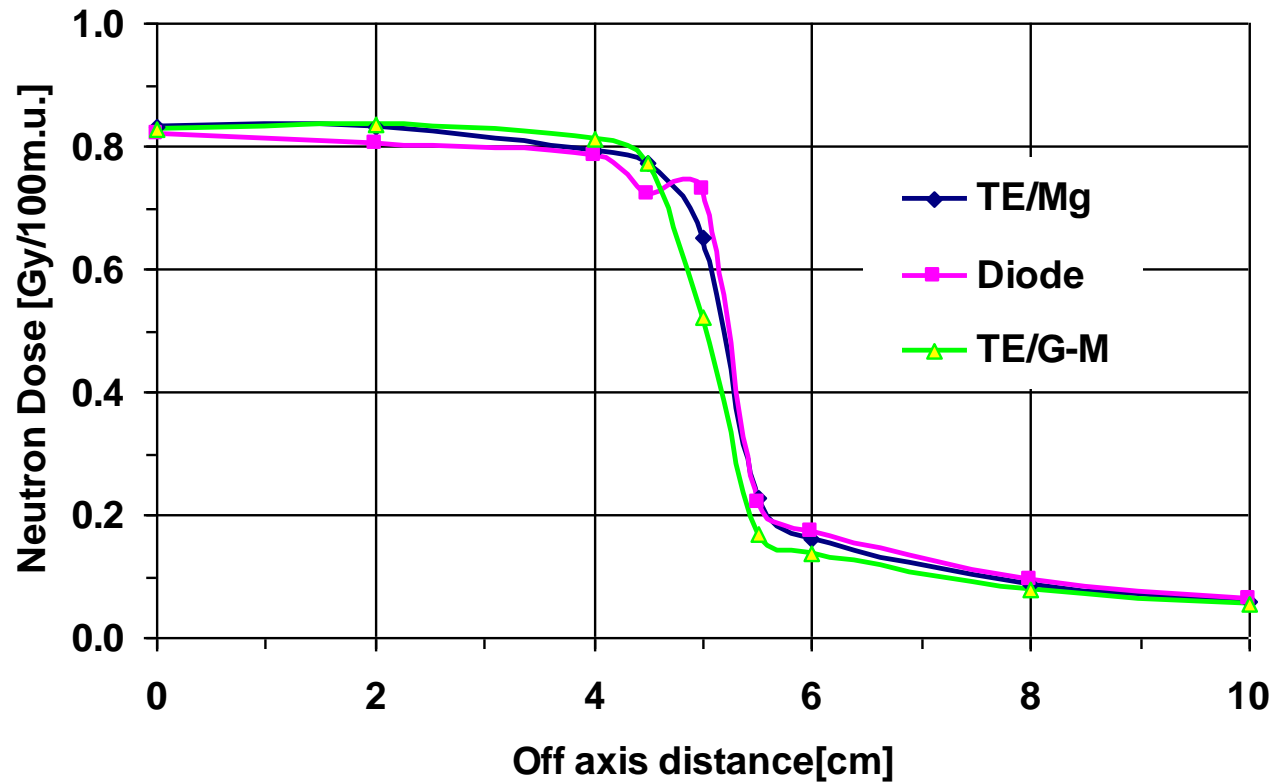
$$R_Q = \frac{R_{nC}}{C_\gamma} \quad \text{and} \quad k_Q = \frac{C_{n,nC}}{C_\gamma}$$

$C_\gamma$  is obtained from the measurements in  $^{60}\text{Co}$  beam

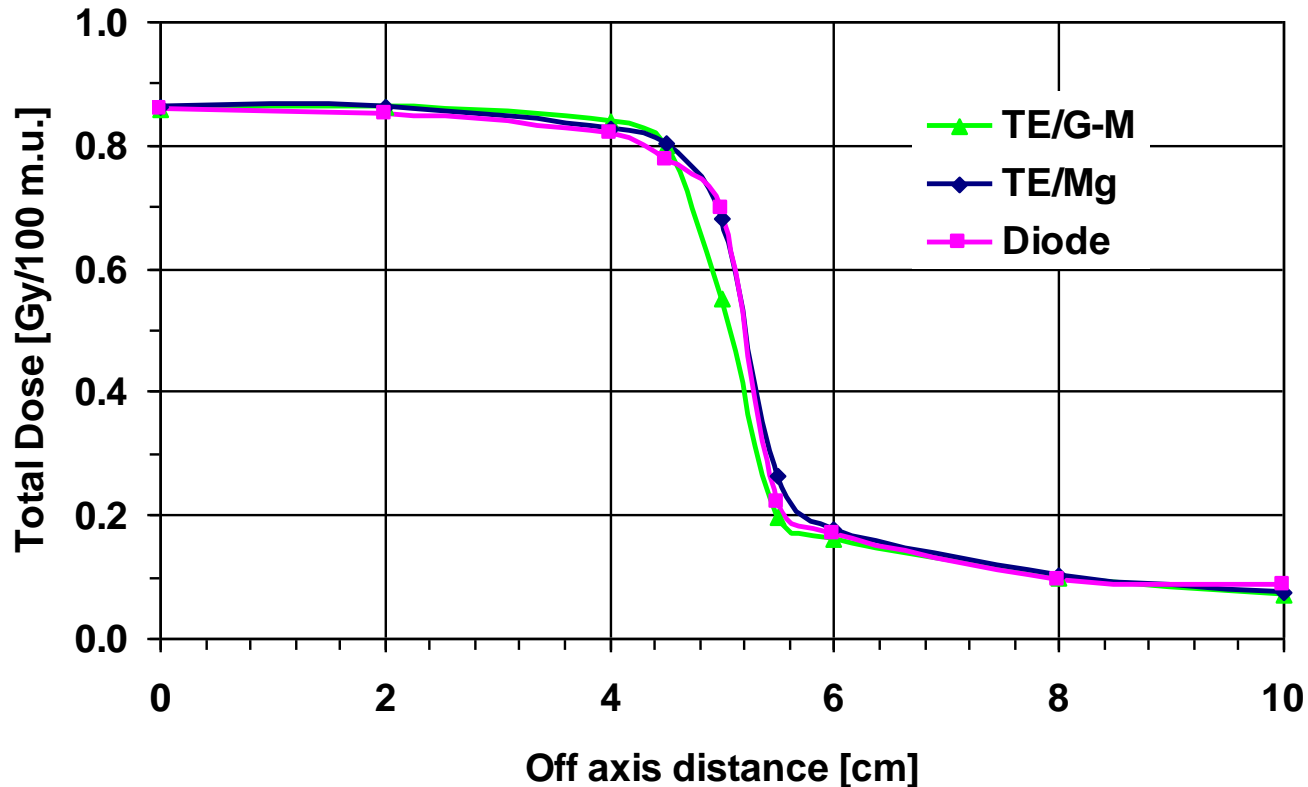
$$C_\gamma = 1.11 \text{ nC/cGy}$$



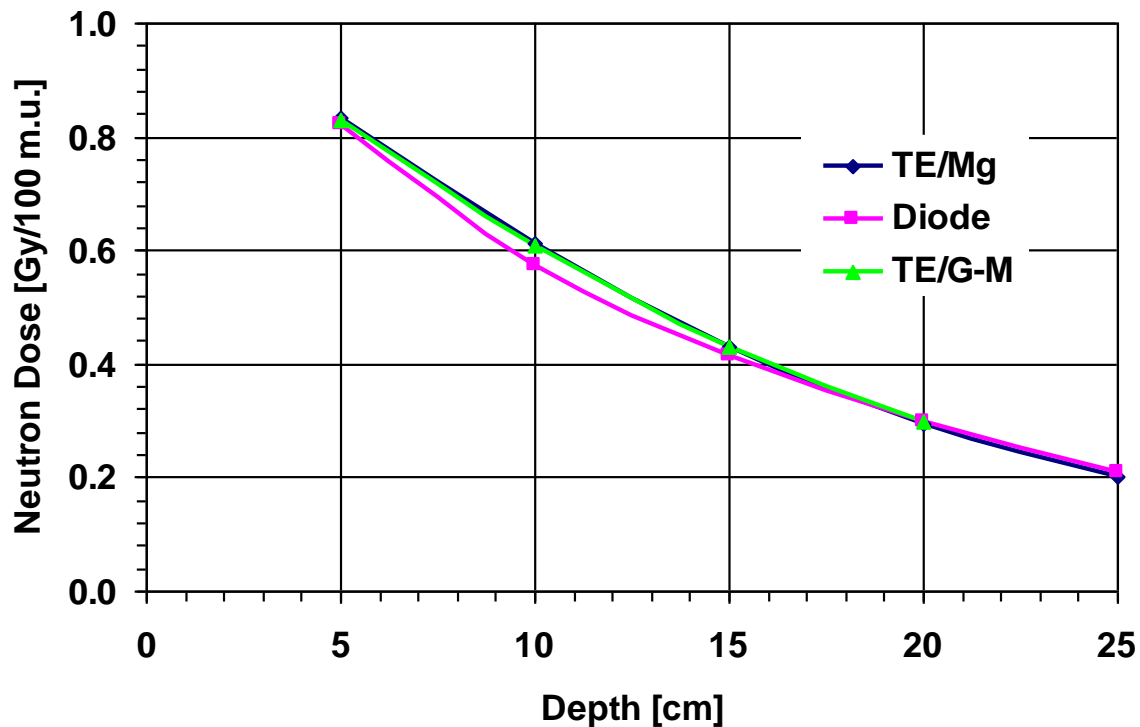
# Lateral Neutron Dose Profile at 5 cm Depth in 10 × 10 cm<sup>2</sup> Field



# Lateral Profile of Total (Neutron + Gamma) Dose at 5 cm Depth in 10 × 10 cm<sup>2</sup> Field

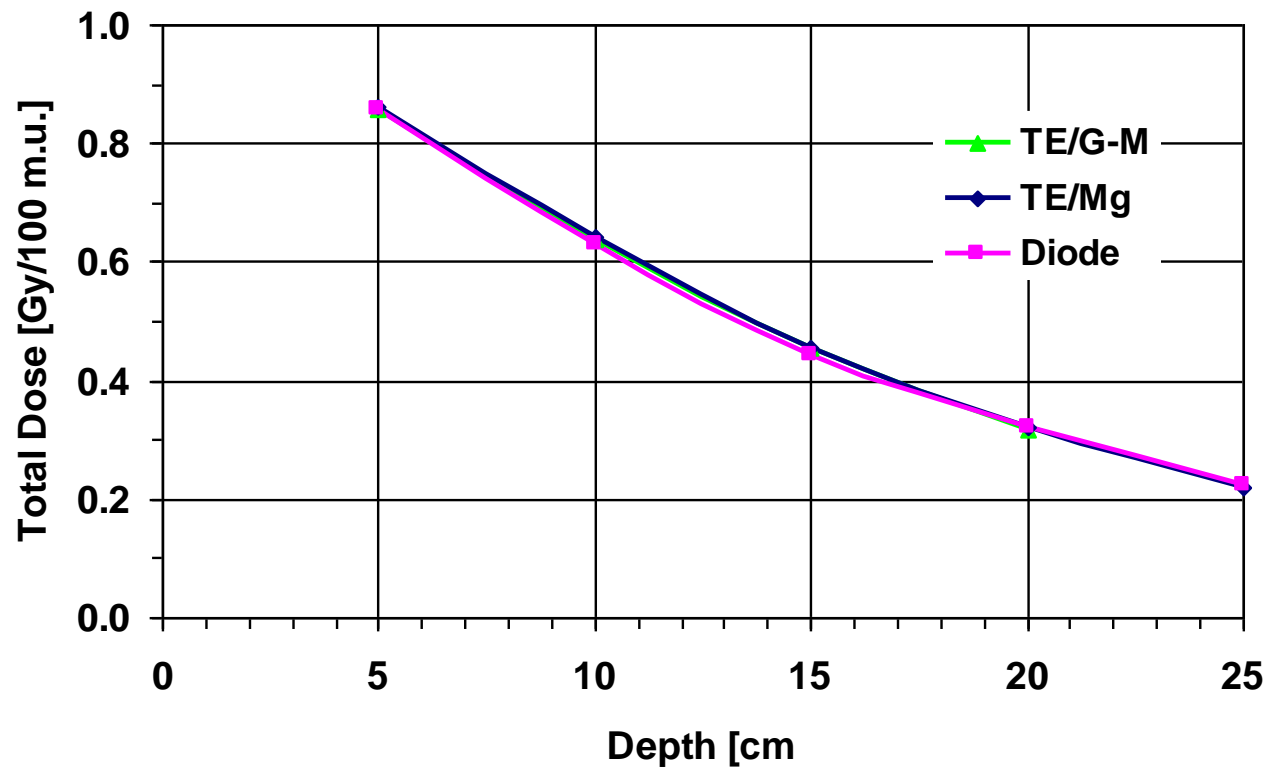


# Neutron Depth Dose Along the Central Axis in $10 \times 10 \text{ cm}^2$ Beam

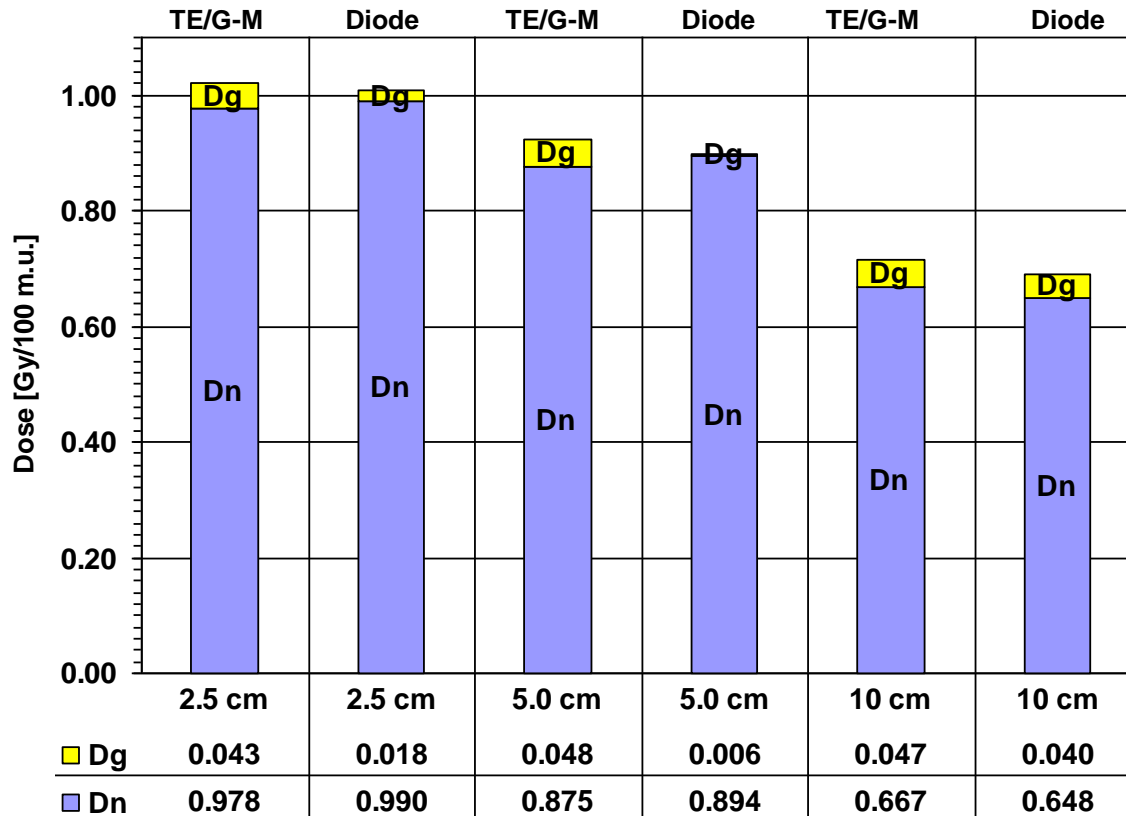




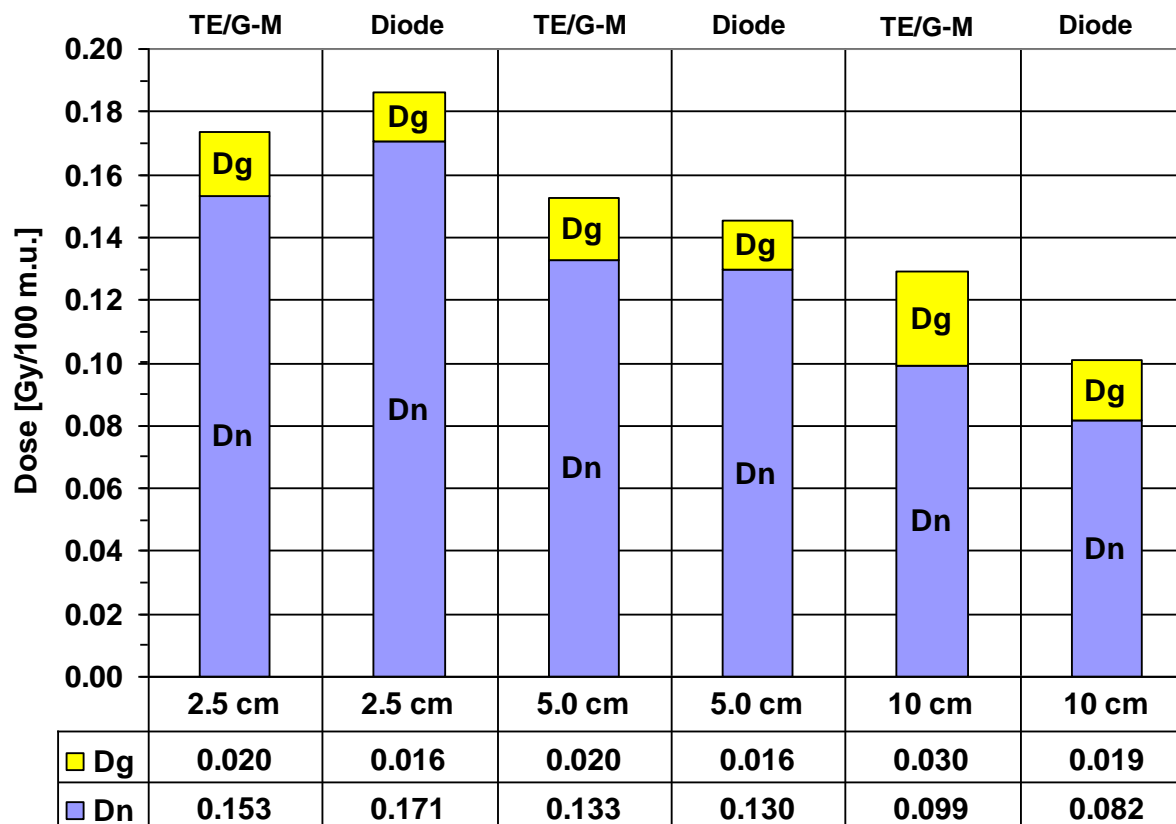
# Total (Neutron + Gamma) Depth Dose Along the Central Axis in $10 \times 10 \text{ cm}^2$ Beam



# TE/G-M Diode Comparison in $15 \times 15 \text{ cm}^2$ Field



# TE/G-M Diode Comparison in Blocked Beam

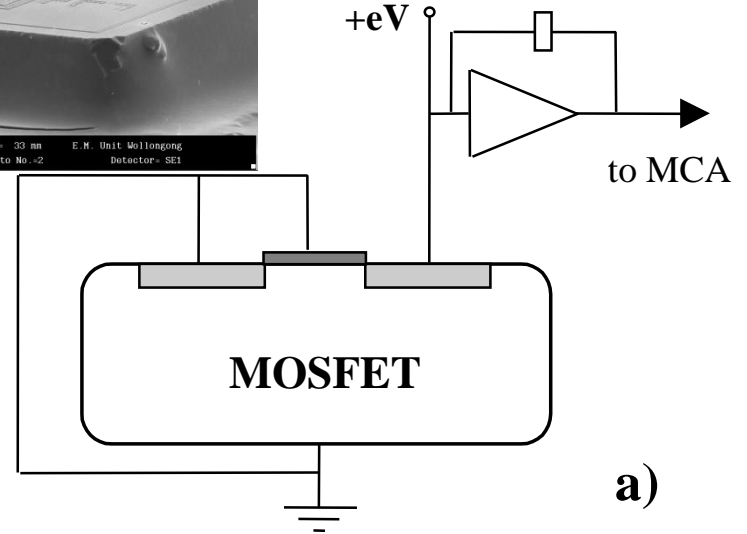
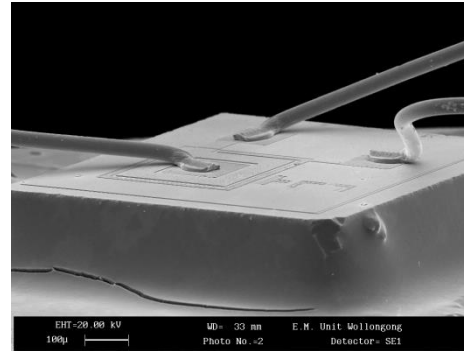
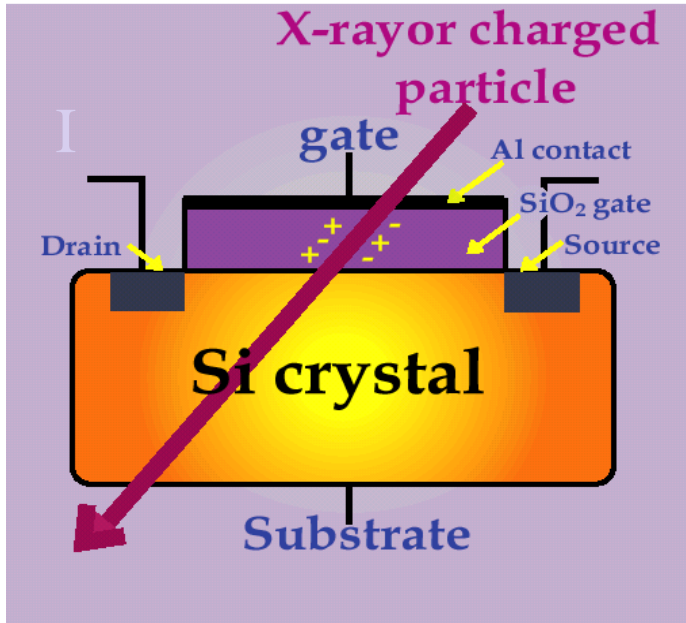


# Conclusion

- ▶ Application of ion implanted *p-I-n* diodes of novel design was investigated in fast neutron beam
- ▶ Operation of the device in “voltage drop” and “charge collection” modes makes it suitable as a twin detector for dosimetry of mixed neutron/gamma beams
- ▶ The sensitivity to neutrons and gamma for both “voltage drop” and “charge collection” modes was defined by the lead attenuation method
- ▶ Total dose together with separate neutron and gamma components were measured at different beam locations as well as under partially blocked collimator
- ▶ The results compare favorable with those obtained with paired TE ionization chamber and G-M counter
- ▶ Further investigation is underway for application of the method in clinical practice

# MOSFET detector Mini- Micro-Dosimetry: generation 1

Simultaneous measurements of stochastic (microdosimetry) and deterministic (absorbed dose) effects at the same location: History of Si Microdosimetry , 1995

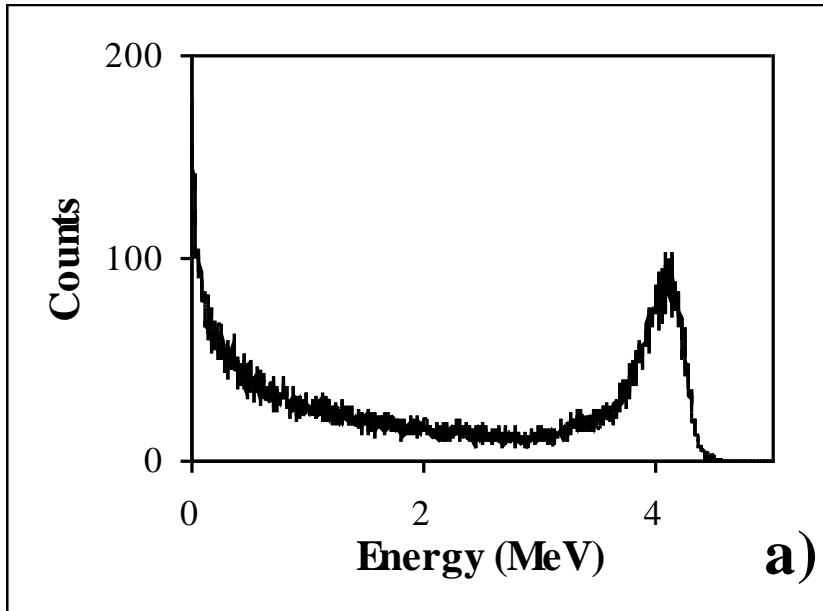


$$\Delta V_{th} = -\frac{eg}{\epsilon_{ox}\epsilon_0} x_c \cdot d_{ox} \cdot f \cdot P \cdot D$$

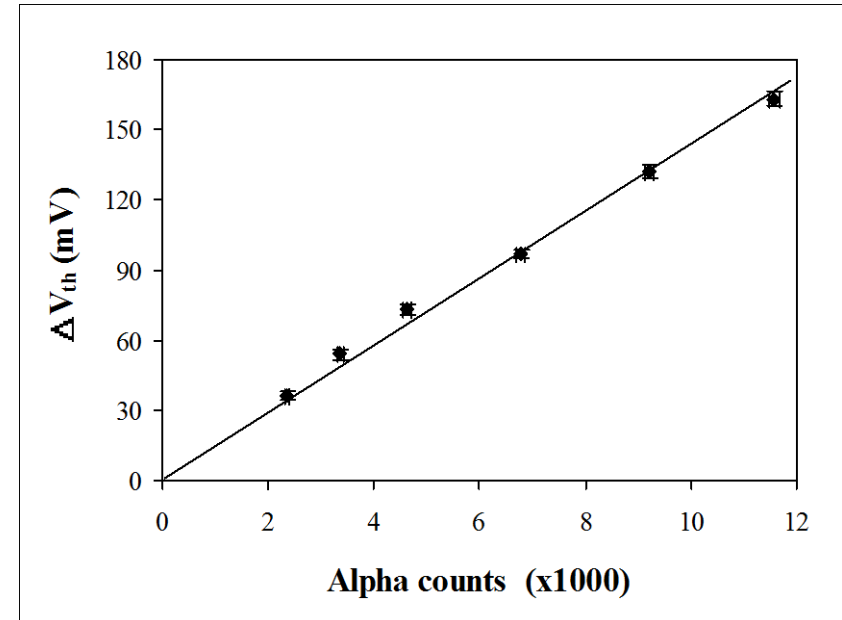
$$\Delta V_{th} \propto D$$

A.Rosenfeld et al. "Simultaneous Macro and Micro Dosimetry with MOSFET" , IEEE TNS **43**, 2693, 1996

# MOSFET detector Mini- Micro-Dosimetry: generation 1

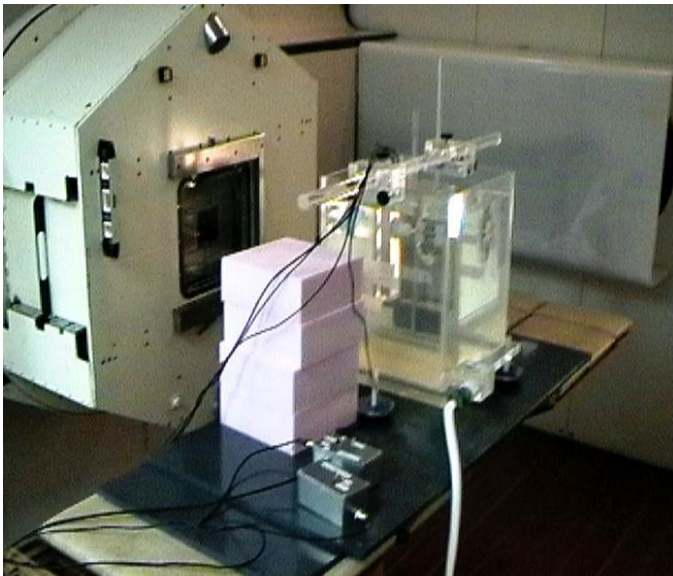
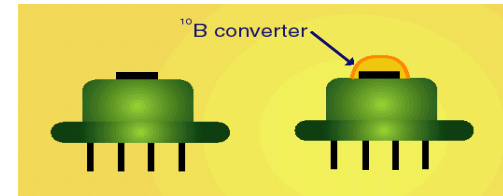


Pulse height spectrum of  $^{241}\text{Am}$  alpha particles deposited at drain p-n junction

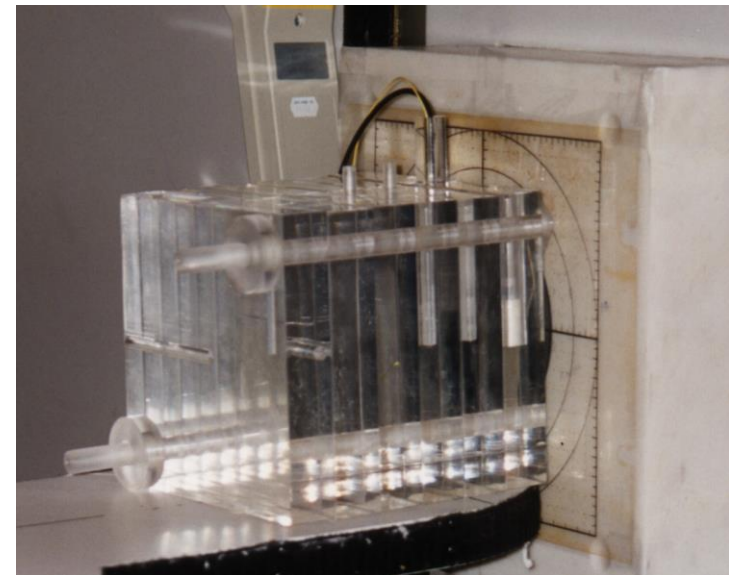


MOSFET threshold voltage change versus number of alpha particles registered in count mode by the same MOSFET

# MOSFET detector Mini- Micro-Dosimetry



FNT facility with MOSFET probe in a water phantom, radiation field 10x10 cm<sup>2</sup>



PMMA slab phantom placed next to the collimator of the epithermal neutron irradiation facility of the BMRR

# MOSFET detector Mini- Micro-Dosimetry: FNT

- ▶ Experiments in a water phantom at FNT facility , USA
- ▶ Average neutron energy 20.4MeV, 10x10 cm<sup>2</sup> field
- ▶ MOSFET probe: simultaneous readout of single event spectra N(E) from the drain p-n junction and relative absorbed dose (V<sub>th</sub>)at different depth

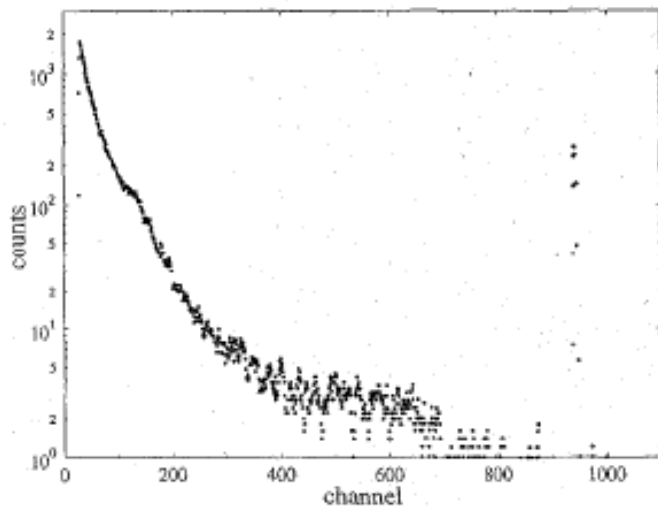


Fig 6. Pulse height spectrum obtained at a depth of 15 cm in the water phantom exposed in FNT neutron beam.

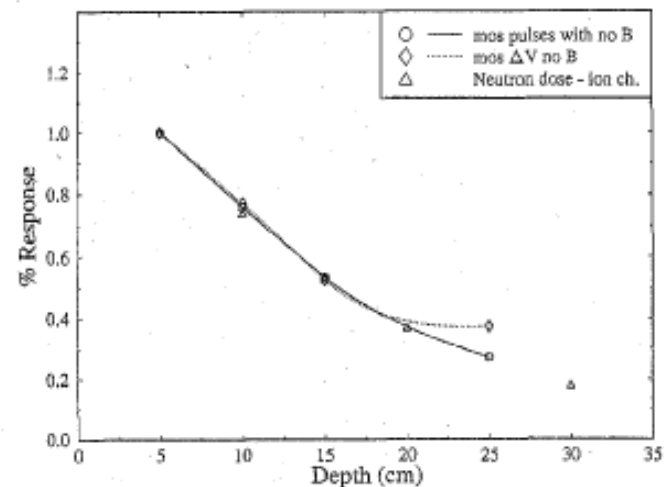
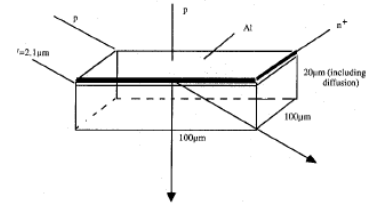


Fig 9 Threshold voltage change of the MOSFET at different depths in the water phantom when exposed in the FNT neutron beam.

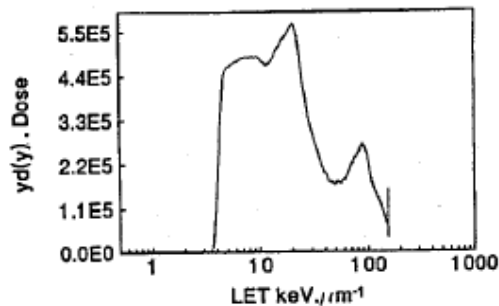


# Microdosimetry with a single micro SV

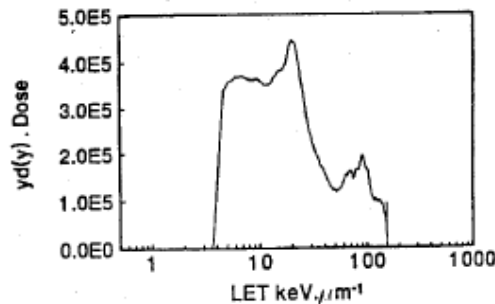
- ▶ RPP SV 100x100x20  $\mu\text{m}^3$  including diffusion
- ▶ Funneling effect-uncertainties in SV
- ▶ Single only SV, efficiency is low
- ▶ Impossible represent cells array



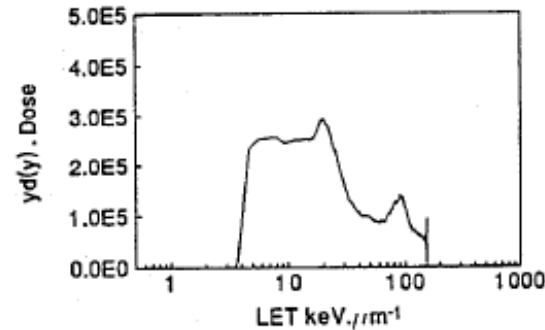
2697



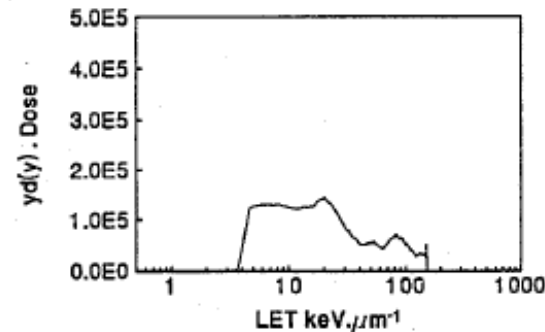
(a)



(b)



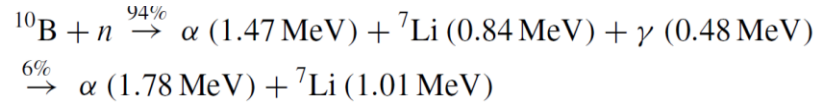
(c)



(d)

Microdosimetric spectra at FNT : depths 5, 10, 15, 20 cm in water

# Future of Accelerator Based BNCT NIS using Liquid Lithium Target



## 1988 - 1996: Updating neutron irradiation system for BNCT using KUR

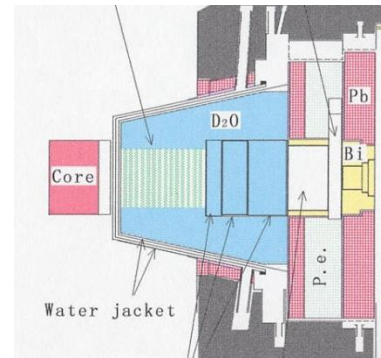
T.Kobayashi, Y.Sakurai, K.Kanda, Y.Fujita and K.Ono, "The Remodeling and Basic Characteristics of the Heavy Water Neutron Irradiation Facility of the Kyoto University Reactor Mainly for Neutron Capture Therapy", *Nuclear Technology*, 131 (2000)

354-378.

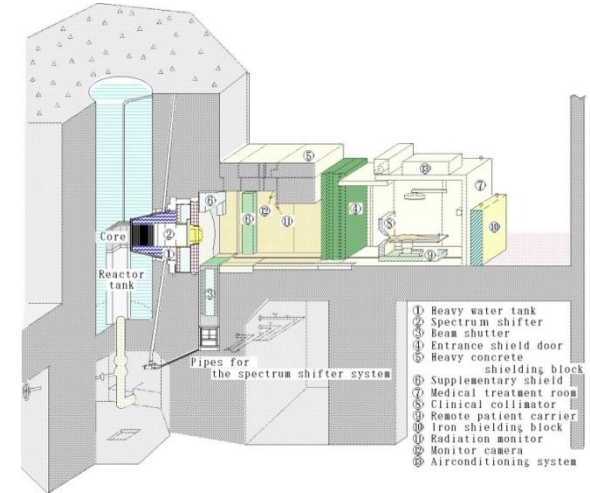
**1988-89** The repair of HWTNF for the leakage of heavy water from the storage tank.

**1990-94** A design study for thermal and epi-thermal neutron irradiation system for BNCT. A Reactor BNCT neutron irradiation system was established.

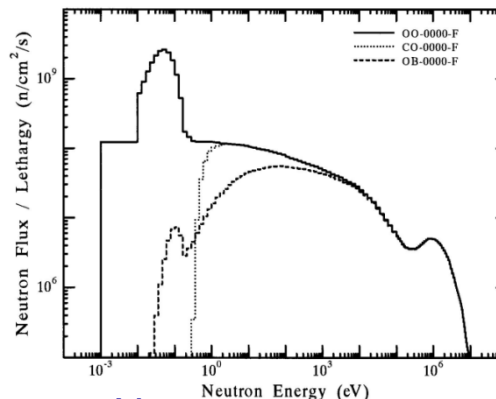
**1995-96** Updating; The convenience of the irradiation technique was improved.



BSA of HWNIF (new)

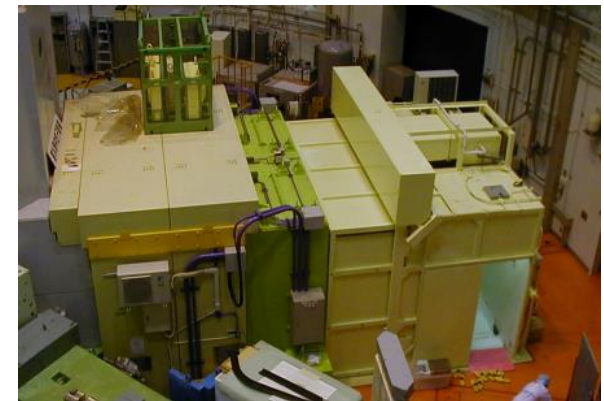


An isometric view of the HWNIF



Neutron energy spectrum

Courtesy of Prof T. Kobayashi



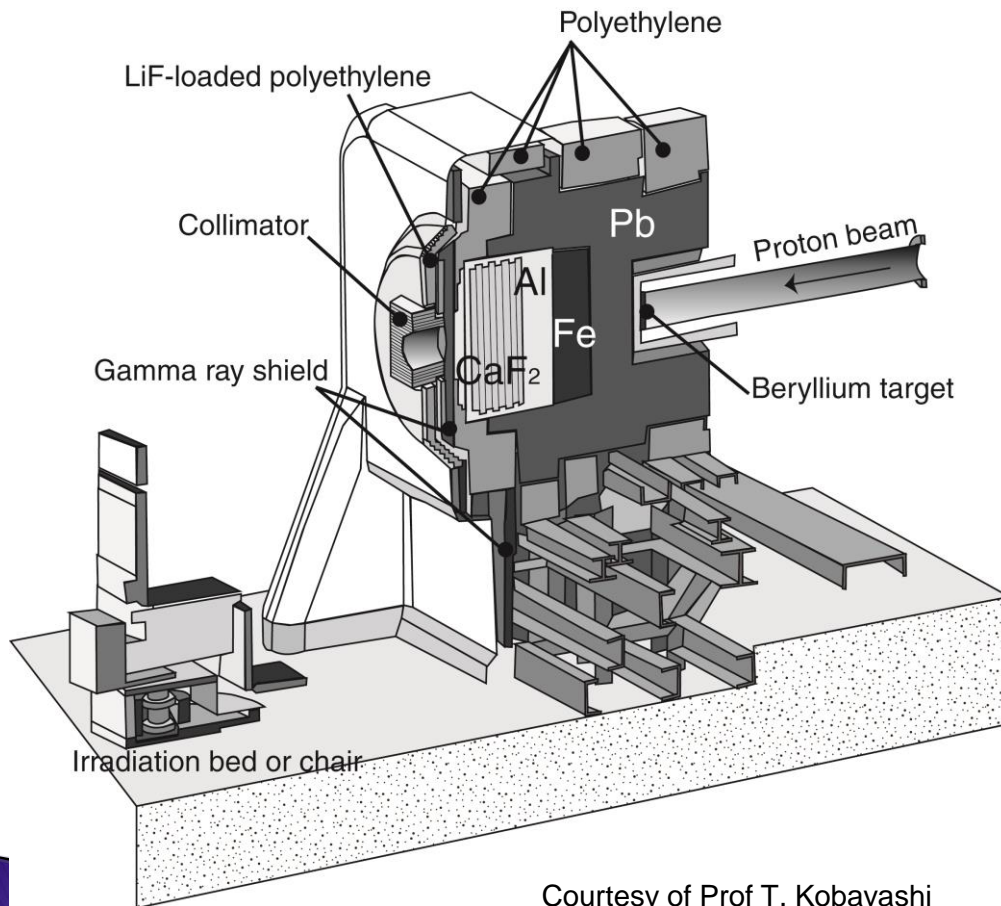
# Cyclotron Based Epi-thermal Neutron Source(C-BENS)

Pb : used as **a breeder and a reflector** for high energy neutrons

Fe : used as **a moderator**

Al and  $\text{CaF}_2$  : used as **a shaper for epi-thermal region**

Polyethylene : used as **a shielding for high energy neutrons**



Courtesy of Prof T. Kobayashi

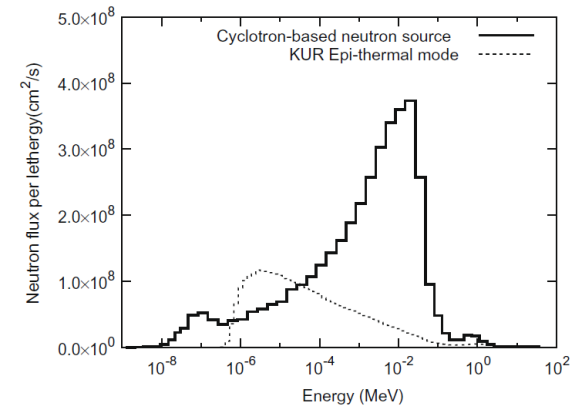


Fig. 6. Comparison with neutron spectrum at a gamma shield for KUR and CBNS.

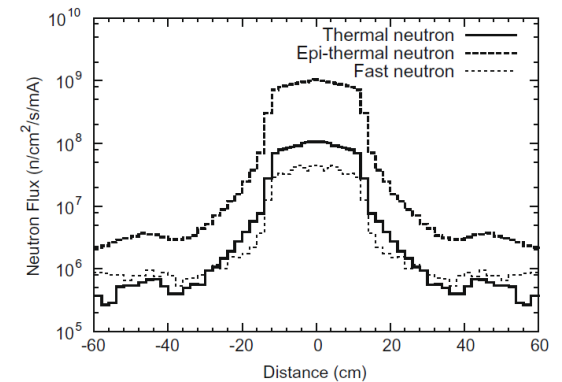
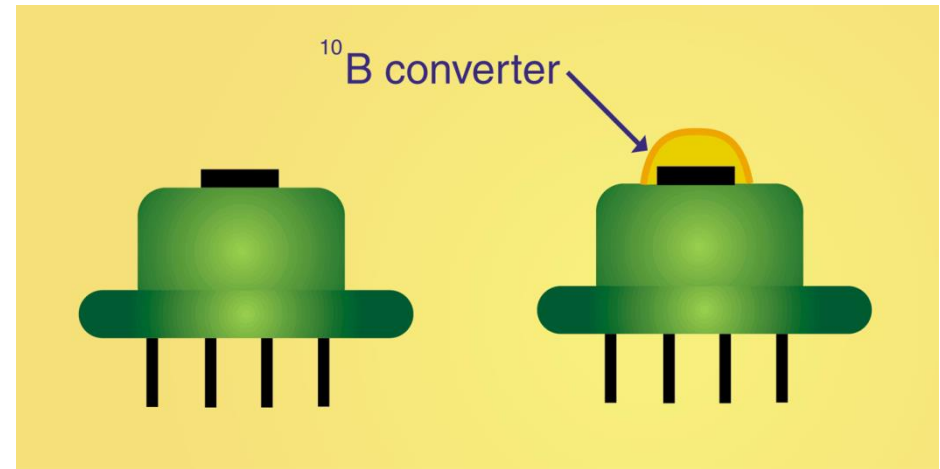
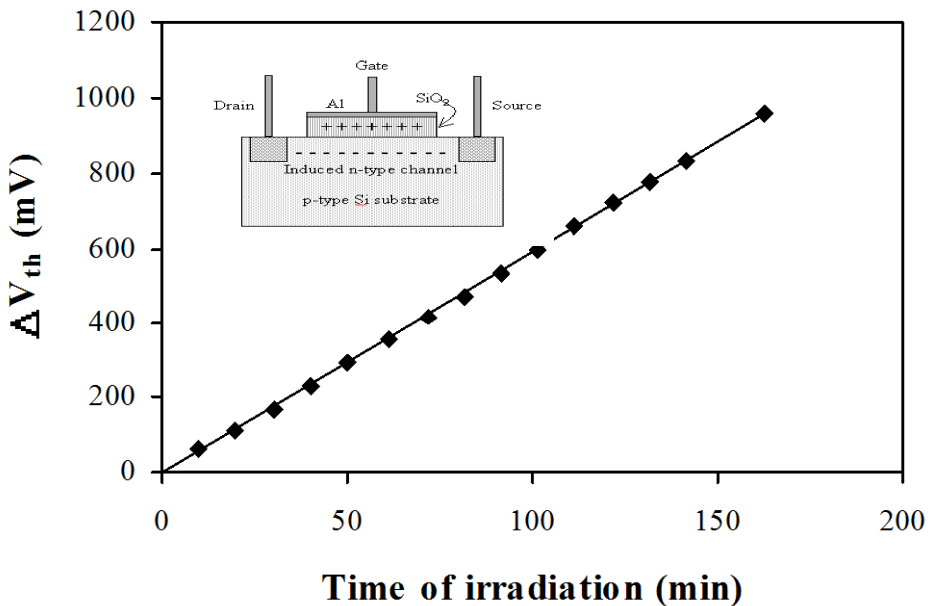


Fig. 7. Flux distribution of thermal, epithermal and fast neutrons as a function of distance from beam axis.

# MOSFET Neutron Dosimetry in BNCT

- ▶ Measurement of thermal neutron flux distribution in a phantom is important for the verification of the dose planning system
- ▶ Measurements of real “Boron-10” response is an advantage as the cross section of Boron-10 is proportional to  $1/v$
- ▶ Online dosimetry using paired MOSFET detectors, both identical detectors produced on the same chip, with one of them covered with the Boron-10 converter

# Paired MOSFET detectors without and with $^{10}\text{B}$ Perspex converter

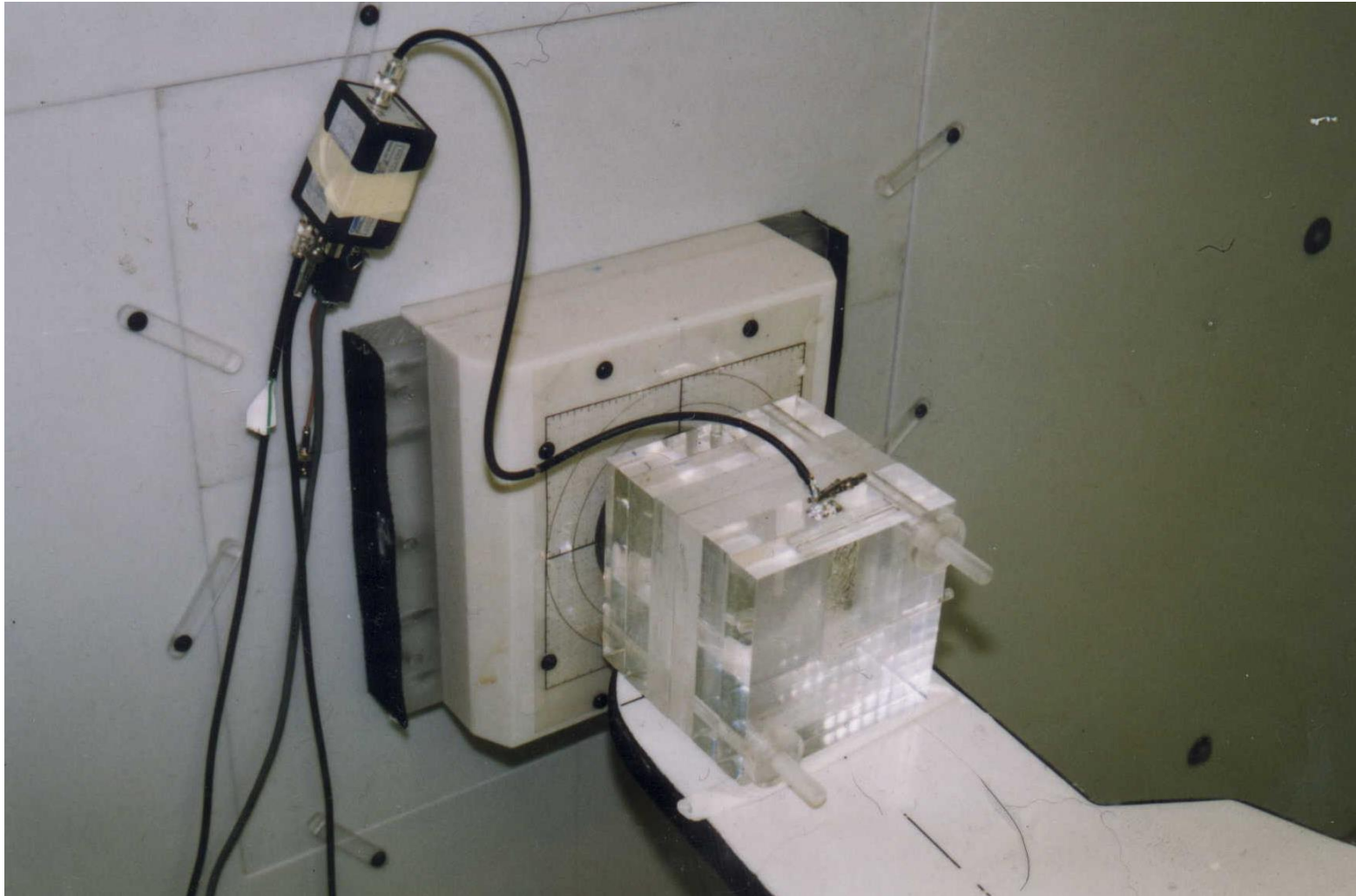


The integral response of an n-MOSFET with a thick oxide layer about 1 micron to 5.48 MeV alpha particles from  $^{241}\text{Am}$  with a fluence of about  $4 \times 10^3 \text{ cm}^{-2}\text{s}^{-1}$

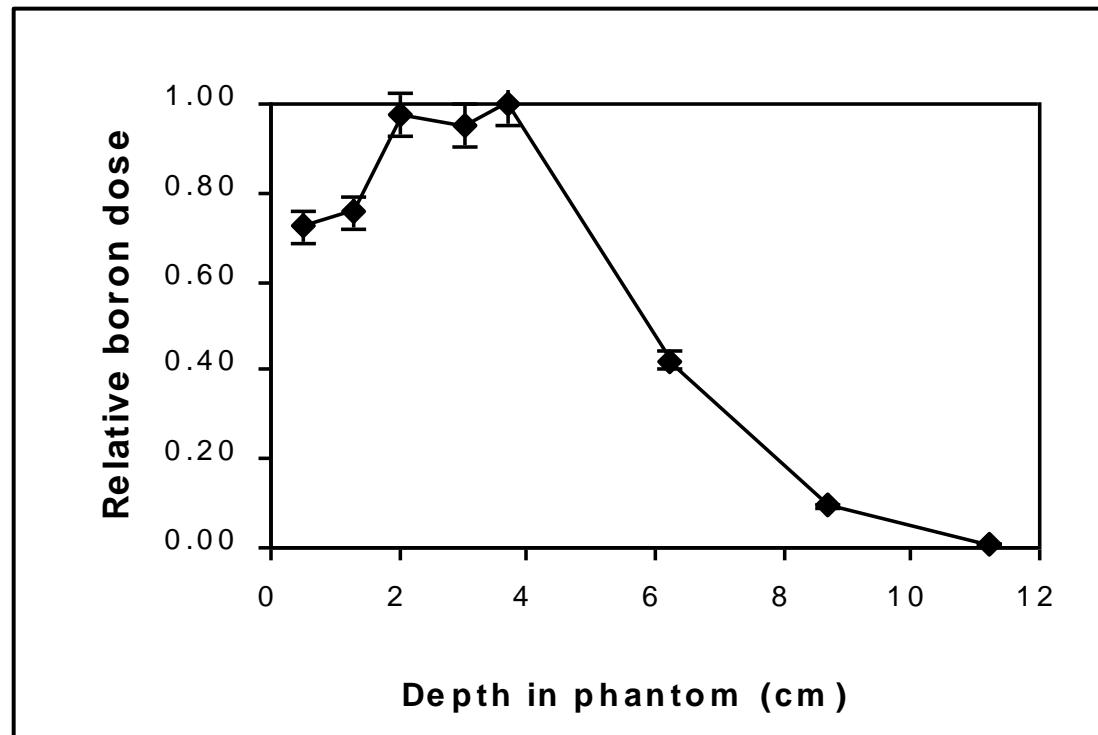
Thermal Neutron Fluence  

$$F = A(\Delta V_{\text{B-10}} - \Delta V)$$

# BNL Epithermal BNCT Facility, Head Phantom



# BNCT at BNL medical research reactor



- ▶ Boron depth dose distribution in a Perspex phantom in a BNCT epithermal neutron beam facility at BNL obtained paired MOSFET detectors with  $^{10}\text{B}$  converter

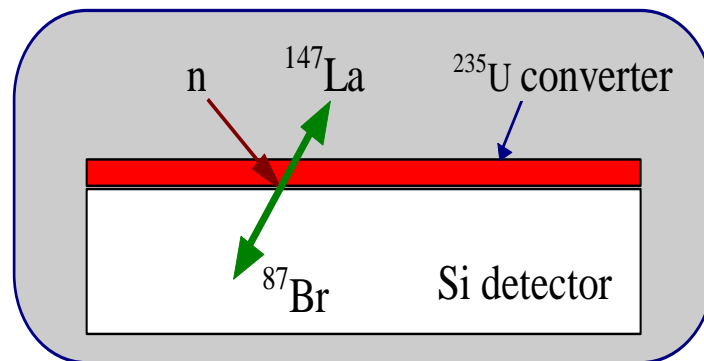
# *p-i-n* Detector with U-235 Converter

## Fission Detector

$^{235}\text{U}$  captures a thermal neutron and fissions with a probability of 85%. The  $^{235}\text{U}$  nucleus splits in about 40 modes. A typical nuclear reaction is

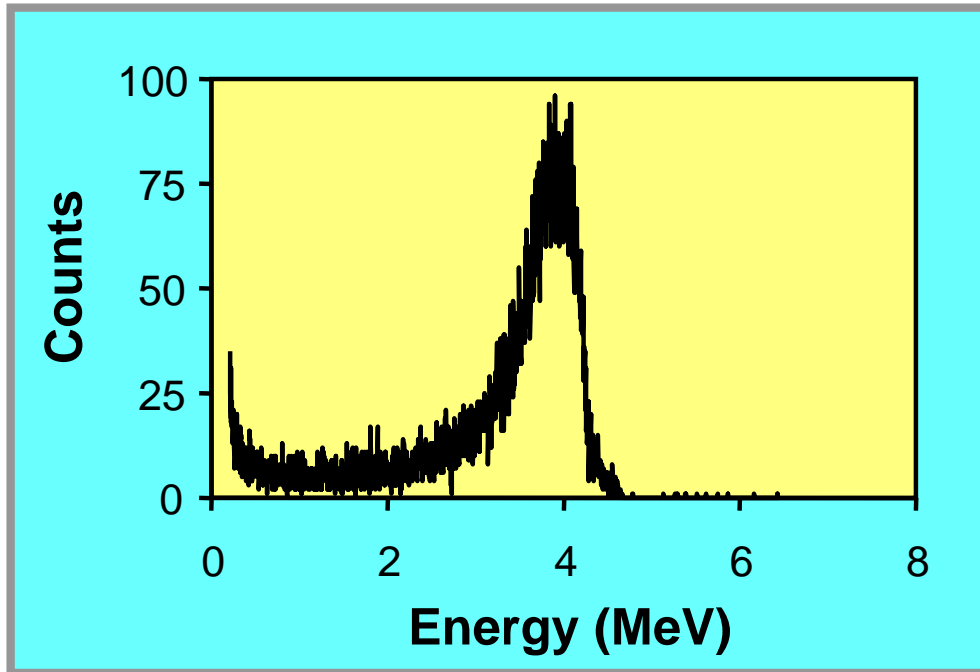


Two fragments carry total kinetic energy of 162 MeV





# $^{235}\text{U}$ Converter on Silicon Detector

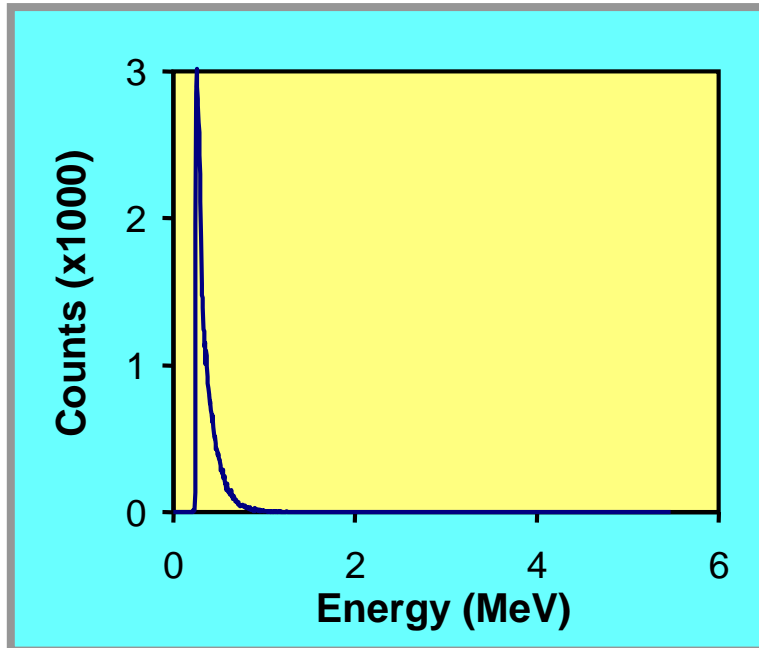


Spectrum of spontaneous alpha decay of  $^{235}\text{U}$  of the fission converter

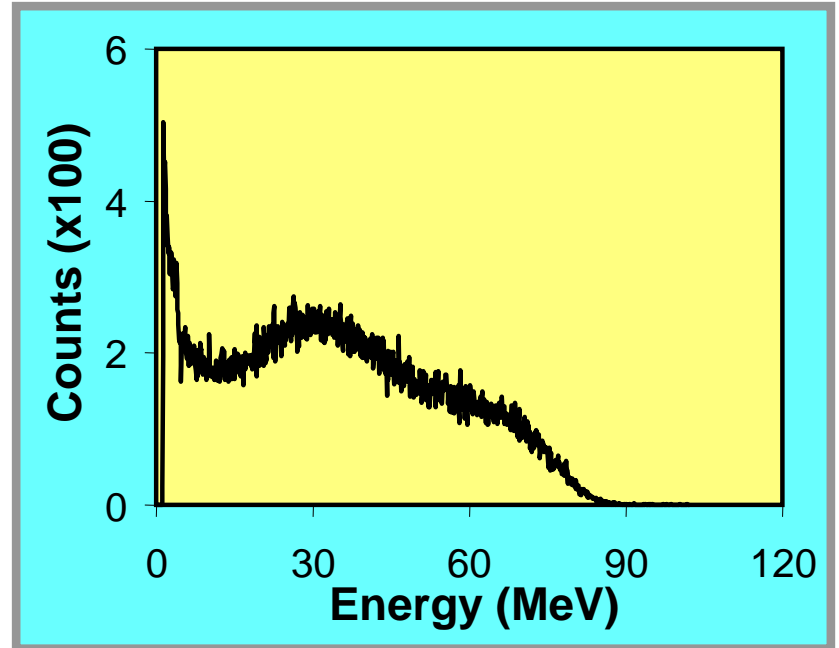
Alpha peak was used for on-line energy calibration and measuring activity of the converter

# Epithermal BNCT at BMRR.

## Pulse height spectra in 15x15x15 cm Perspex phantom



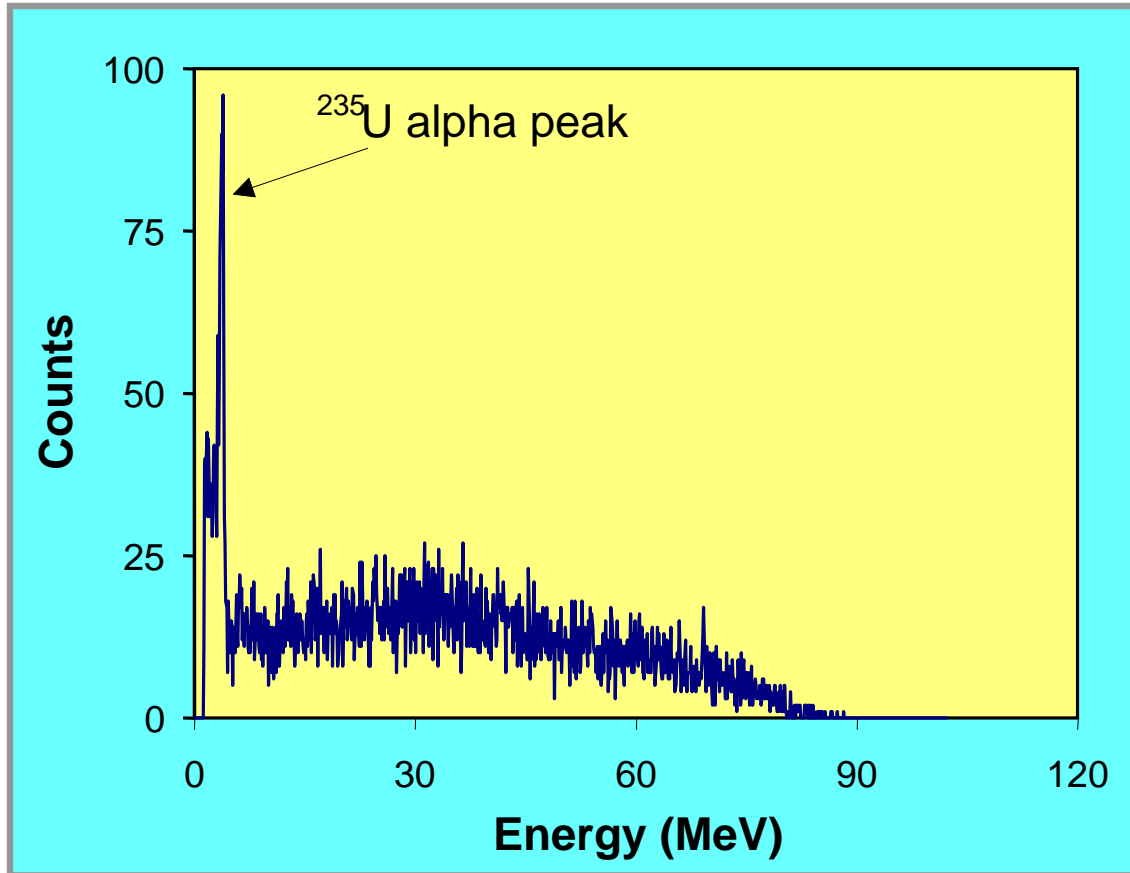
Silicon detector spectrum, without the fission converter, at 3.7 cm depth in the phantom



Fission detector spectrum at 3.7 cm depth in the phantom

# Epithermal BNCT at BMRR.

## Pulse height spectrum in 15x15x15 cm Perspex phantom



Thermal neutron fluence is given by

$$\phi = N_f / (\sigma \cdot N_u \cdot p)$$

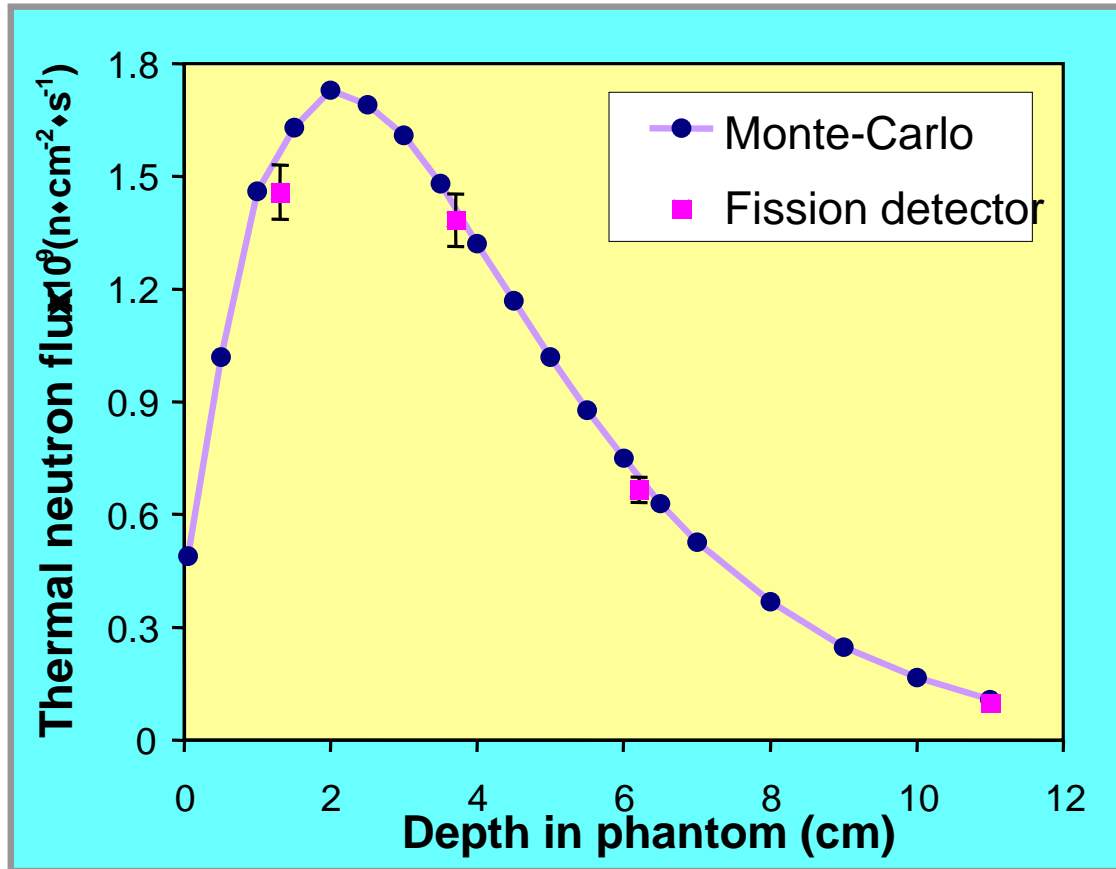
$p=0.85$  is the fission probability

$N_u$  is the number of U-235 converter

$N_f$  is the number of fragments – area under the spectrum  
 $\sigma$  is the cross section

Fission detector spectrum at 11 cm depth in the phantom

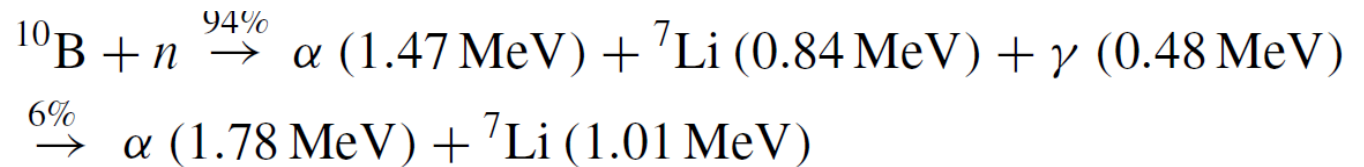
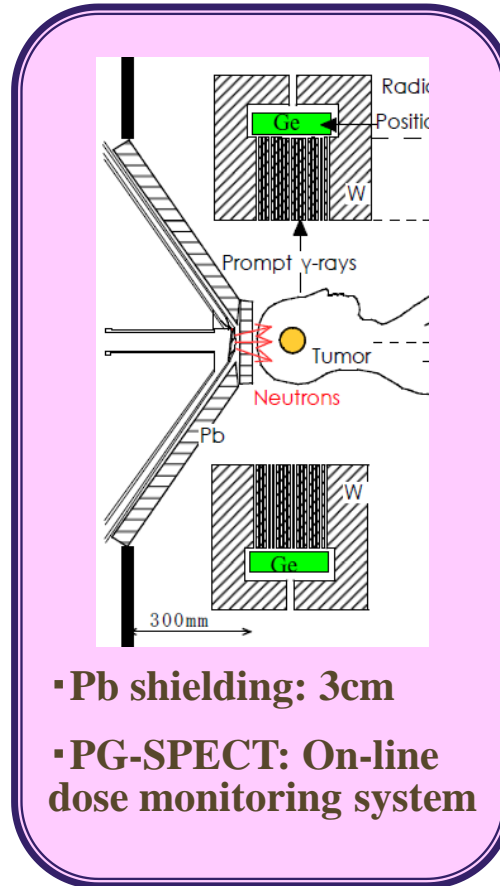
# Thermal Neutron Flux in Perspex Phantom



Monte Carlo calculated and fission detector measured thermal neutron flux along the Perspex phantom central axis. BMRR, BNCT facility, 3 MW.

# On Line Boron Dose Dosimetry in BNCT

## BNCT System



Courtesy of Prof T. Kobayashi

# Non-Tissue Equivalent Detectors for Monte Carlo Verification

- ▶ *p-i-n* diodes have been found to be useful for the verification of Monte Carlo simulation of phantom neutron spectra in epithermal BNCT
- ▶ Approach-
  - Running MCNP to simulate the neutron spectra at any depth in the phantom
  - Simulate damage kerma at any point in the phantom using simulated spectrum
  - Verify damage kerma experimentally through the placement of diodes in the phantom which are calibrated in terms of damage kerma

$$\Delta V = \alpha \int_0^E K(E_n) \Phi(E_n) dE_n$$

$K(E_n)$  is based on ASTM data

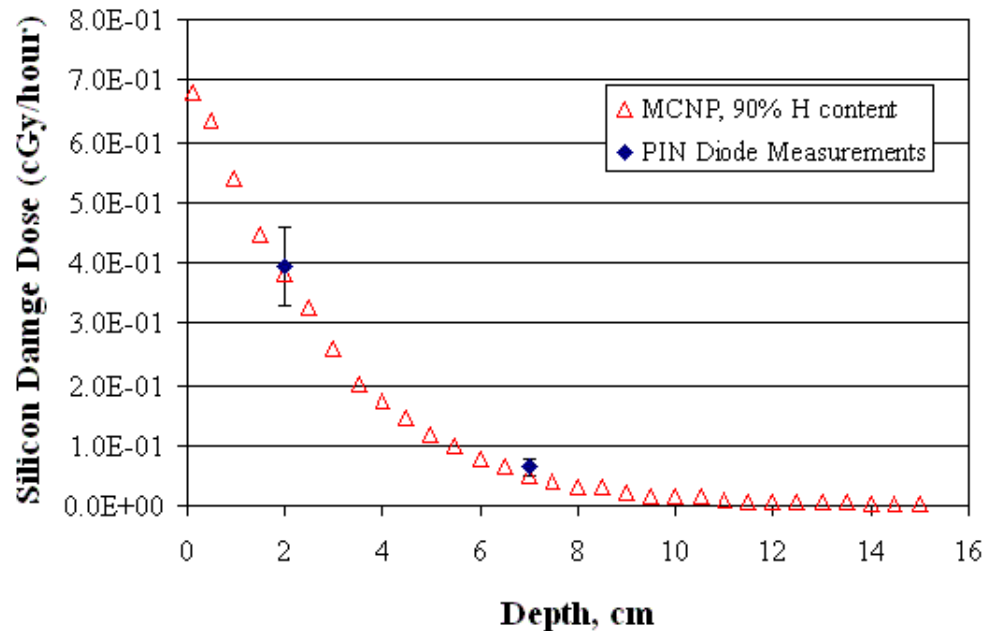
$\Phi(E_n)$  the neutron spectra of HB 11 beam at the point of irradiation in free air geometry

$\alpha$  is a calibration coefficient

$\Delta V$  is a forward voltage shift of Si diode under investigation

# Experiment at HB11 Epithermal Beam, Patten

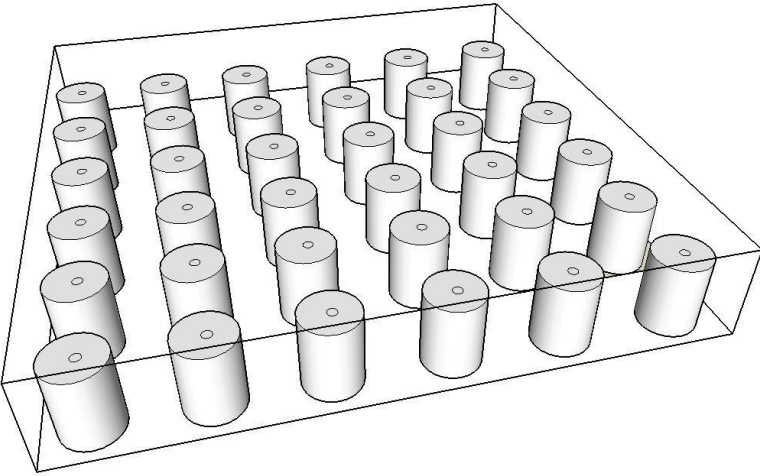
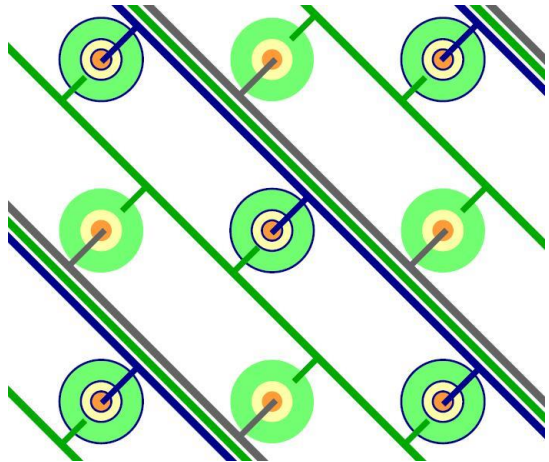
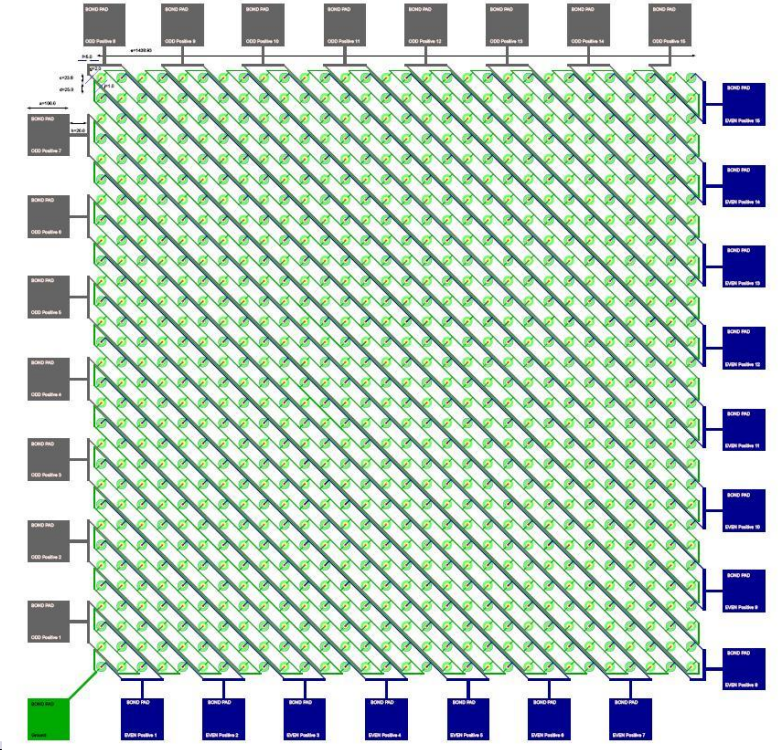
- ▶ The simulated dose rate at the point of calibration was  $0.576 \text{ cGy(Si) h}^{-1}$  and determined the average calibration factor as being  $214.9 \text{ mV cGy}^{-1}(\text{Si})$  with a 5% spread across 14 diodes



# 3D SOI silicon microdosimetry

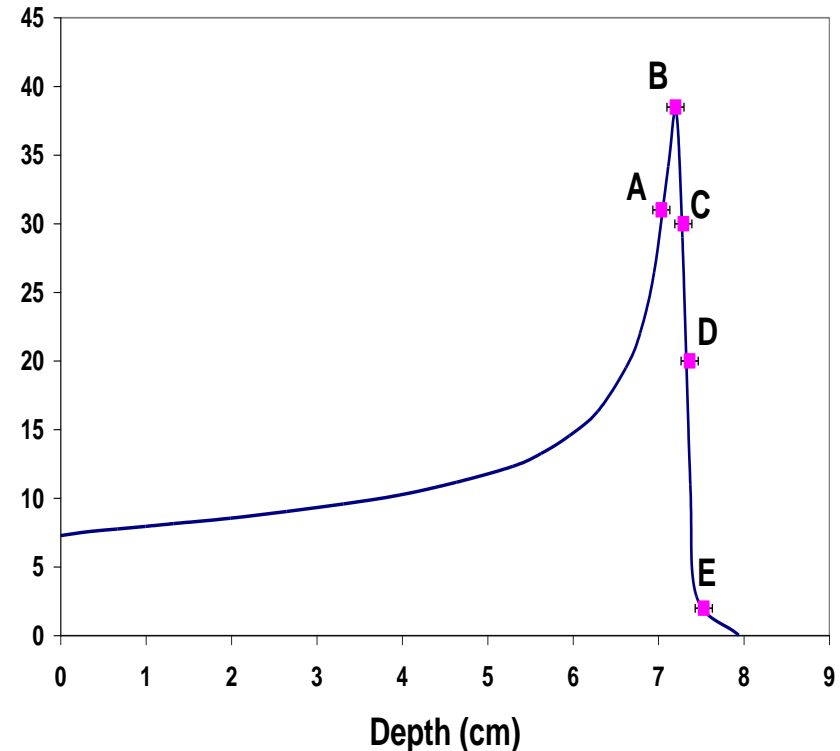
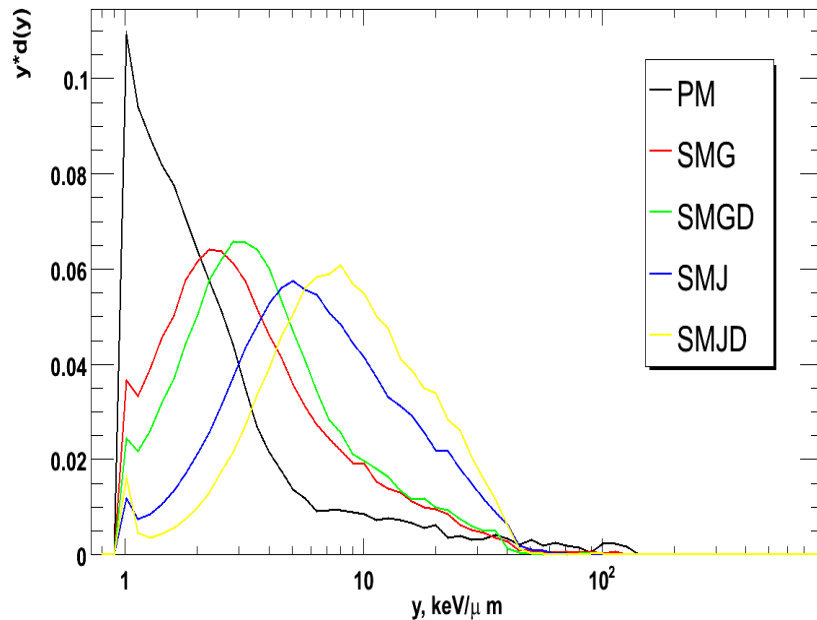
- 3D silicon cell array for modeling of energy deposited in biological cells event by event by secondaries
- Each Si cell is 6x10 microns

Detector Array Design\_3(Revised) (All dimensions are in microns)  
 Number of cells: 30x30  
 Detector Array dimension: 1430um x 1430um  
 Bond Pad dimension: 100um x 100um  
 Diameter of each cell: 22.2 um  
 Spacing between cells: 25 um





# SOI Microdosimetry on 100 MeV Proton Therapy



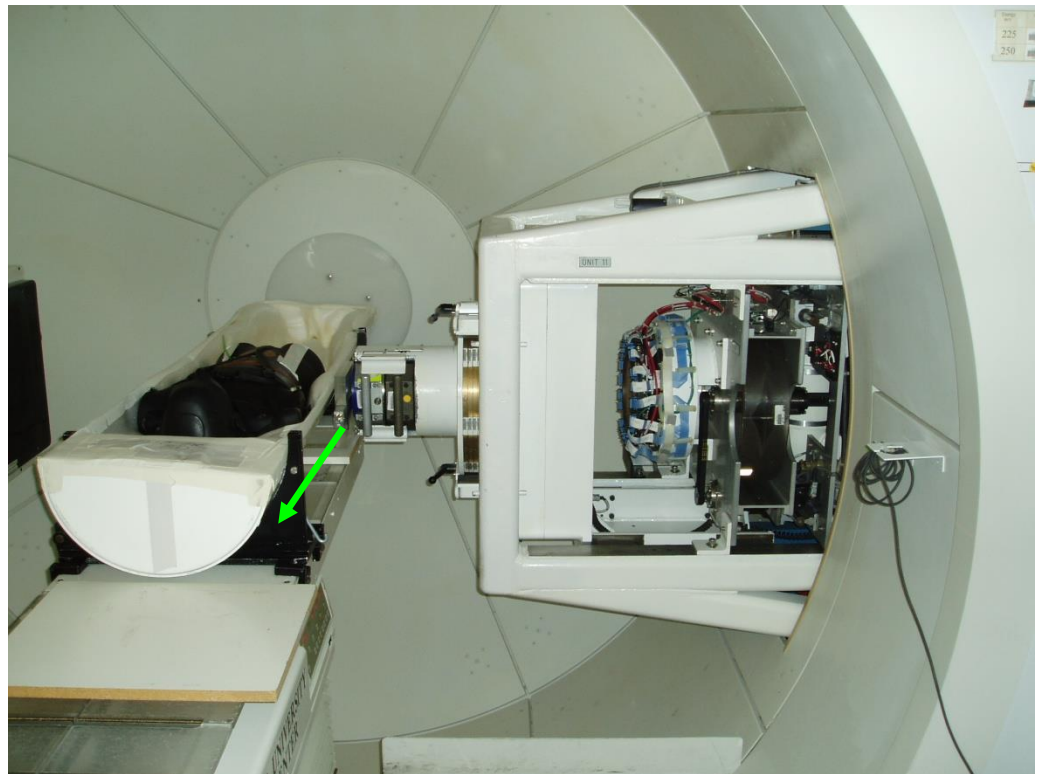
- ▶ Microdosimetric spectra from 10 mm SOI micro at consecutive positions in a Bragg Peak
- ▶ Possibility to estimate Q of the beam

For more details see: A Rosenfeld "Electronic Dosimetry in Radiotherapy",  
Rad. Meas., 41, 134-153, 2007



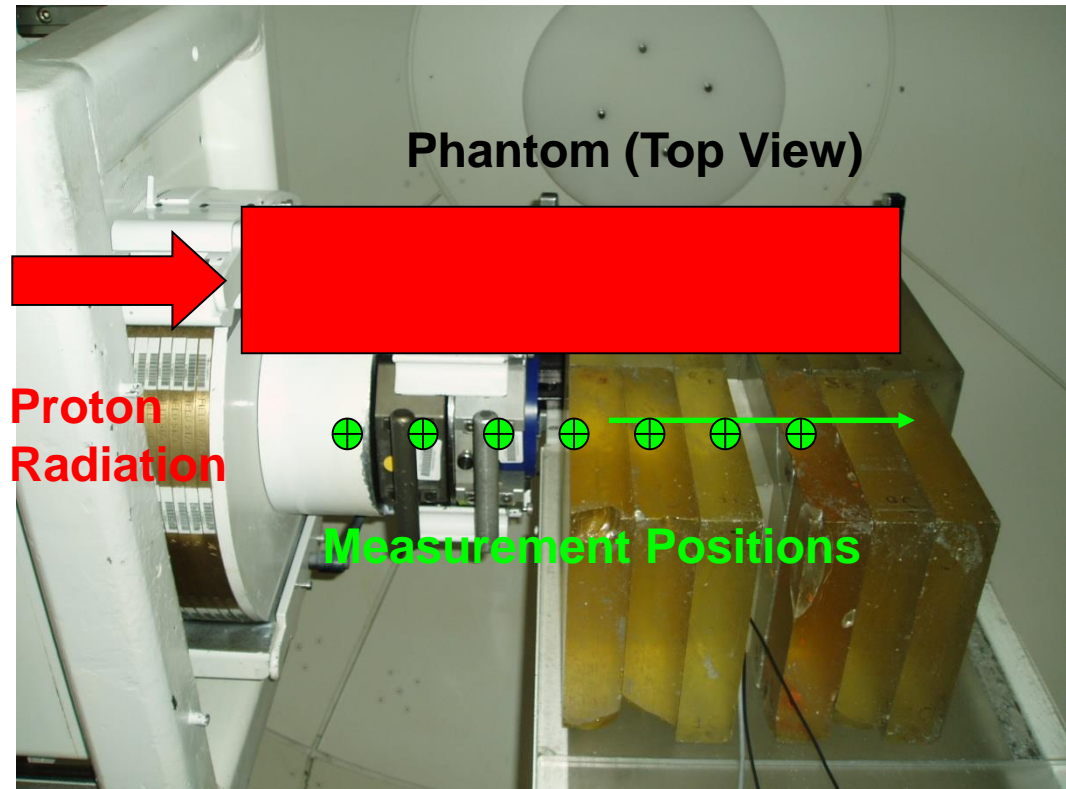
# Experimental Setup

- ▶ Prostate treatment conditions replicated
- ▶ The microdosimeter was moved laterally with respect to the field edge
- Device centred to the height of the central axis
- Incident protons of 225MeV were utilised

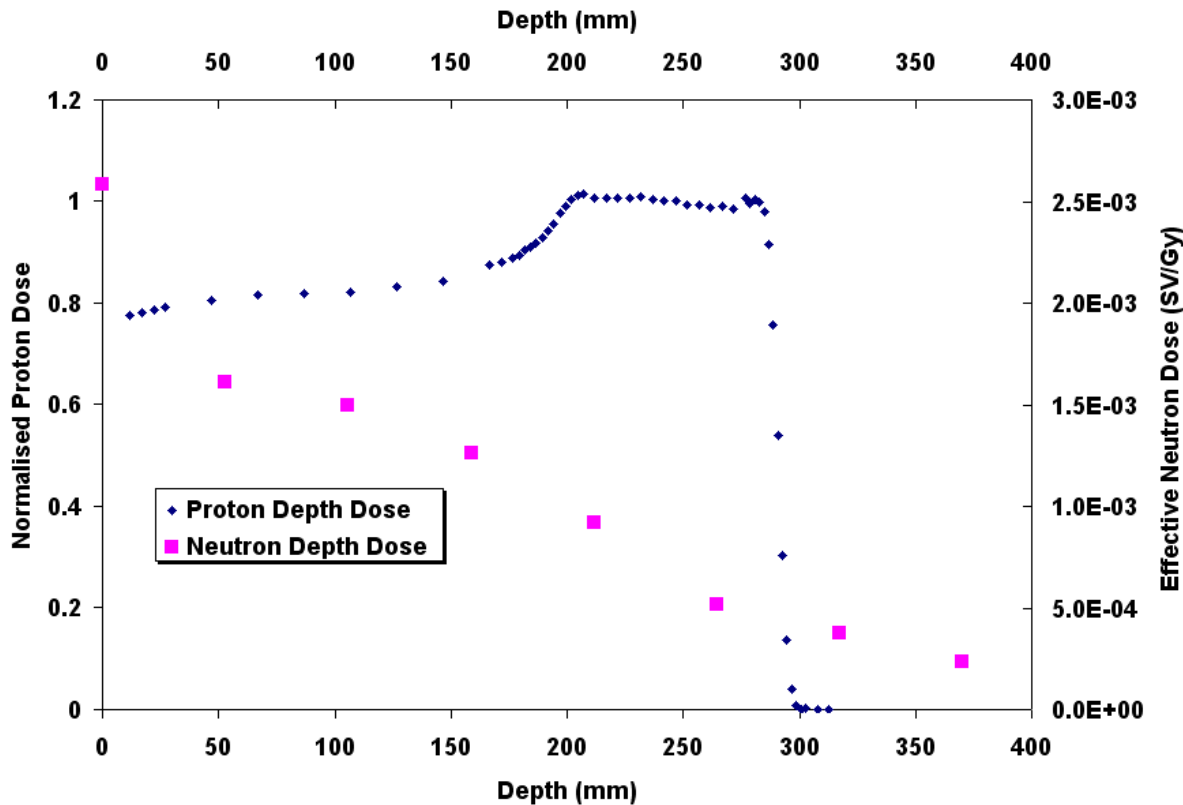


# Experimental Setup

- ▶ The microdosimeter was moved parallel to the central beam axis 5cm from the field edge.
- The device was centred to the height of the central axis
- Incident protons of 225MeV were used.



# Proton Therapy- secondary cancer risk estimation



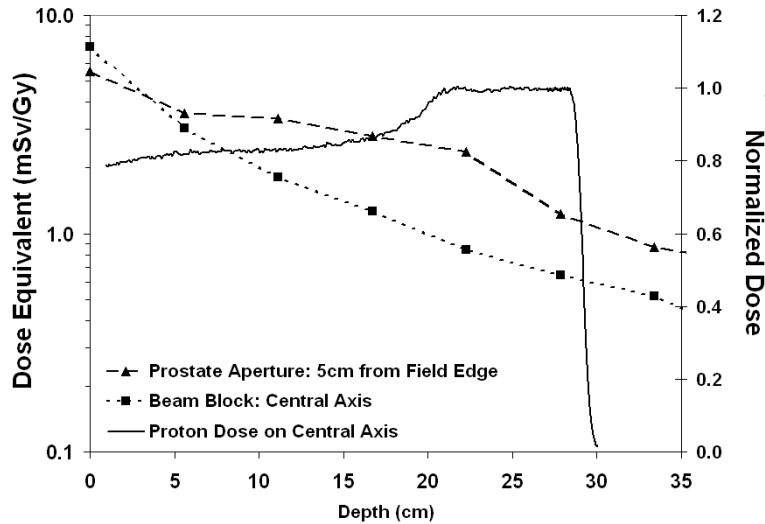
CMRP: Firstly measured dose equivalent with silicon SOI microdosimetry.

- Invited in phantom experiments were carried out at LLUMC and MGH proton therapy facilities

- All typical cancer treatment scenario with PT were investigated

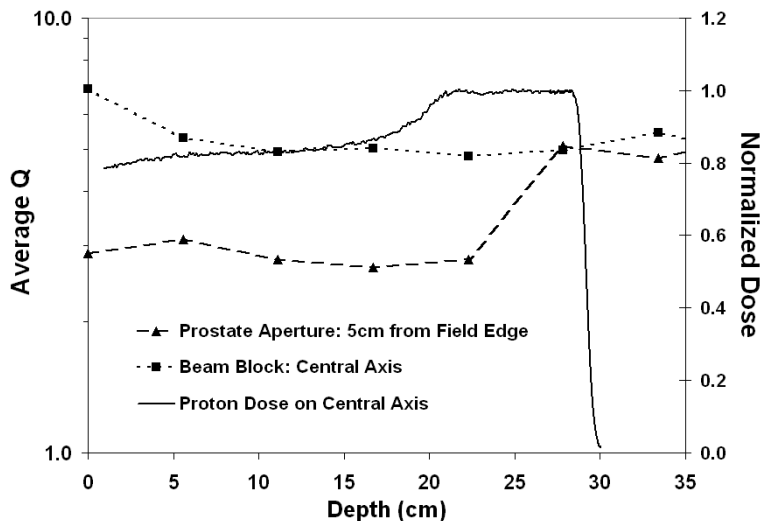
- Measured dose equivalent was less than predicted that make confirmation of safety of PT

# Results

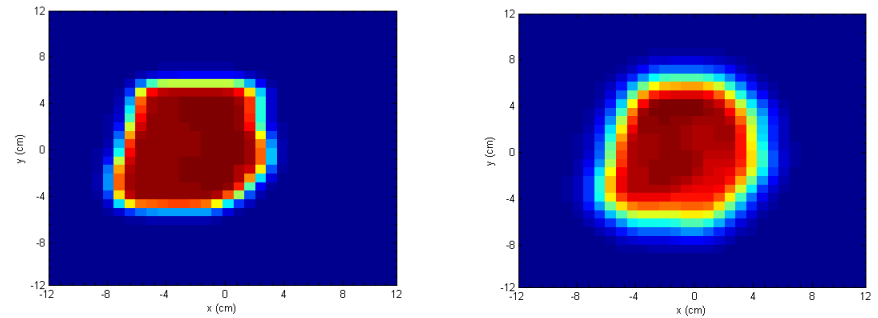
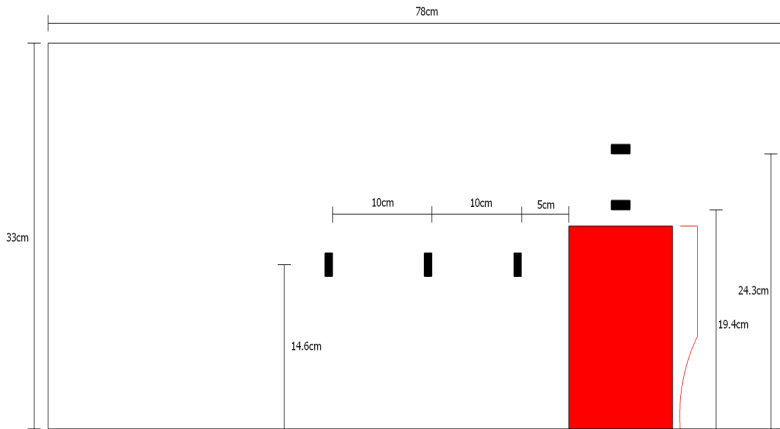


Scanning parallel to the beam at 5cm offset

- ▶  $0.9 \text{ mSv/Gy} < H_{\text{aperture}} < 5.5 \text{ mSv/Gy}$
- ▶  $0.5 \text{ mSv/Gy} < H_{\text{block}} < 7.1 \text{ mSv/Gy}$
- ▶  $H_{\text{aperture}}$  has a different dependence on depth than  $H_{\text{block}}$
- ▶ Scattered primary protons affects H and the determination of Q up to 22.3 cm depth
- ▶ Downstream of the Bragg peak, difference in H is due to n generated in the phantom



# $\Delta E$ -E telescope: PBS vs Double Scattering

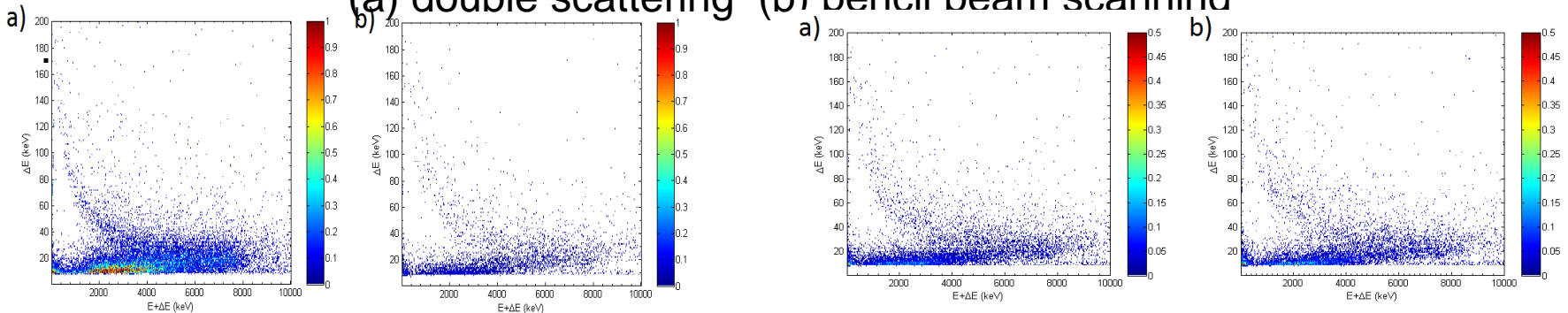


Beam shape for the double scattering (left) and pencil beam scanning (right) fields using the MatriXX detector (IBA dosimetry)

The 5 measurement positions of the  $\Delta E$ -E detector during the experiment.

$\Delta E$ -E spectra downstream of SOBP, on a the central axis:

(a) double scattering (b) pencil beam scanning



19.4cm depth

25 cm depth

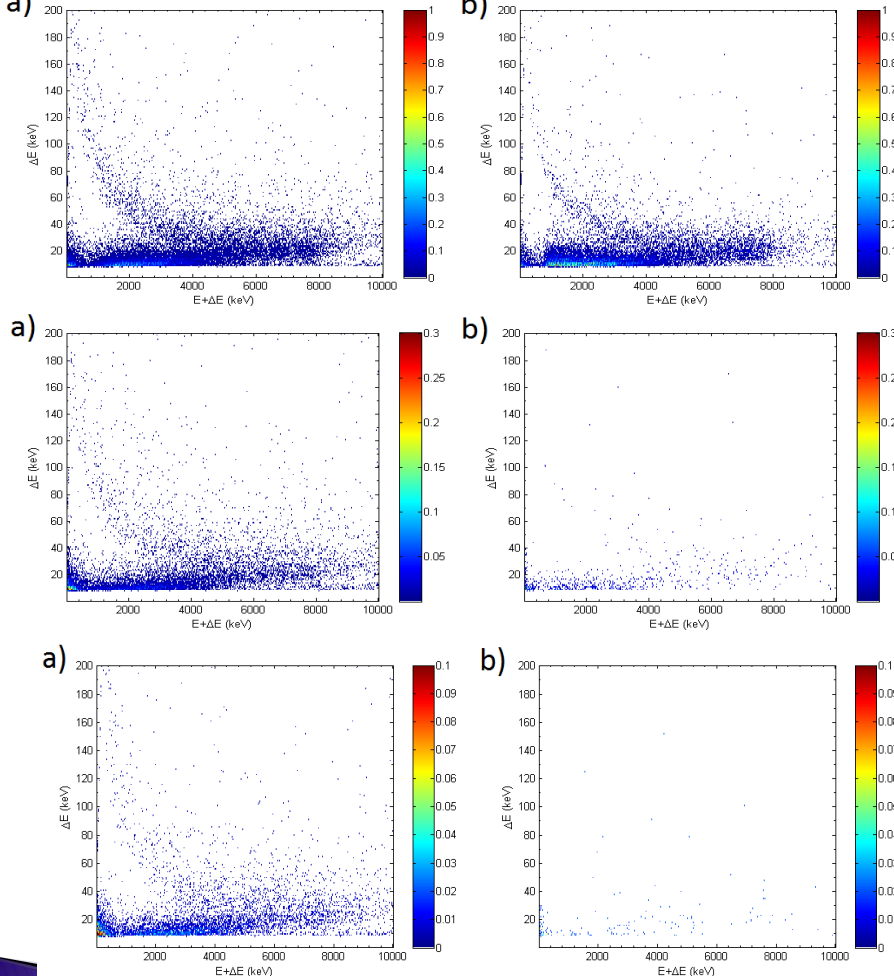
Stephen Dowdell, PhD Thesis, CMRP UoW, May 2011

with B.Clasie, J.Flanz, A.Fazzi, A.Pola, S.Agosteo, A.Rosenfeld

# $\Delta E$ - $E$ telescope: PBS vs Double Scattering

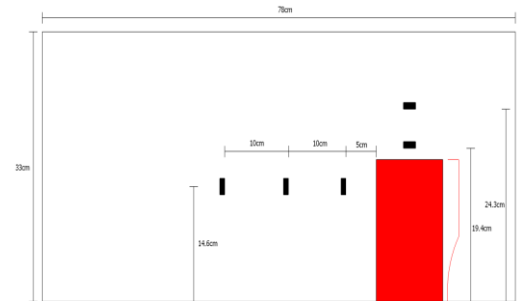
$\Delta E$ - $E$  spectra at a depth of 14.6cm in Lucite normalized counts/Gy in SOBP

a) double scattering; b).pencil beam scanning



Lateral distance from the field edge

5 cm



15 cm

- Direct confirmation of essential reduction of neutrons laterally out of field for PBS vs passive delivery

25 cm

- Closer to the field contribution from scattered protons for PBS higher due to larger penumbra in comparison with passive delivery

# X-ray Medical LINAC





# Photoneutron Production ( $\gamma, n$ ) reactions

Component	15 MeV	18 MeV	20 MeV
Target	9 % (W,Cu)	16 % (W,Cu)	17.2% (W,Cu)
Primary Collimator	38% (W)	41% (W)	36% (W)
Flattening Filter	22% (W)	9% (Fe,Ta)	10.4% (Fe,Ta)
Jaws	29% (W)	35% (W)	36% (W)
Other (shielding, etc)	1.20%	1.40%	1%

Table 1: Monte Carlo calculation of the % of photoneutron production

in various linac component's for a Varian 2100/2300C Linac. [1, Mao]

Maximum Photon Energy (MeV)	Average Neutron Energy (MeV)
15	1.15
18	1.25
20	1.31
25	1.46

Table 2: Average photo-neutron energies for high-energy Linacs. [2, Facure]



Figure 1: Varian 18MV Medical Linac cross section view. [3]

# Photo-Neutron Energy Spectrum in a Radiotherapy Treatment room

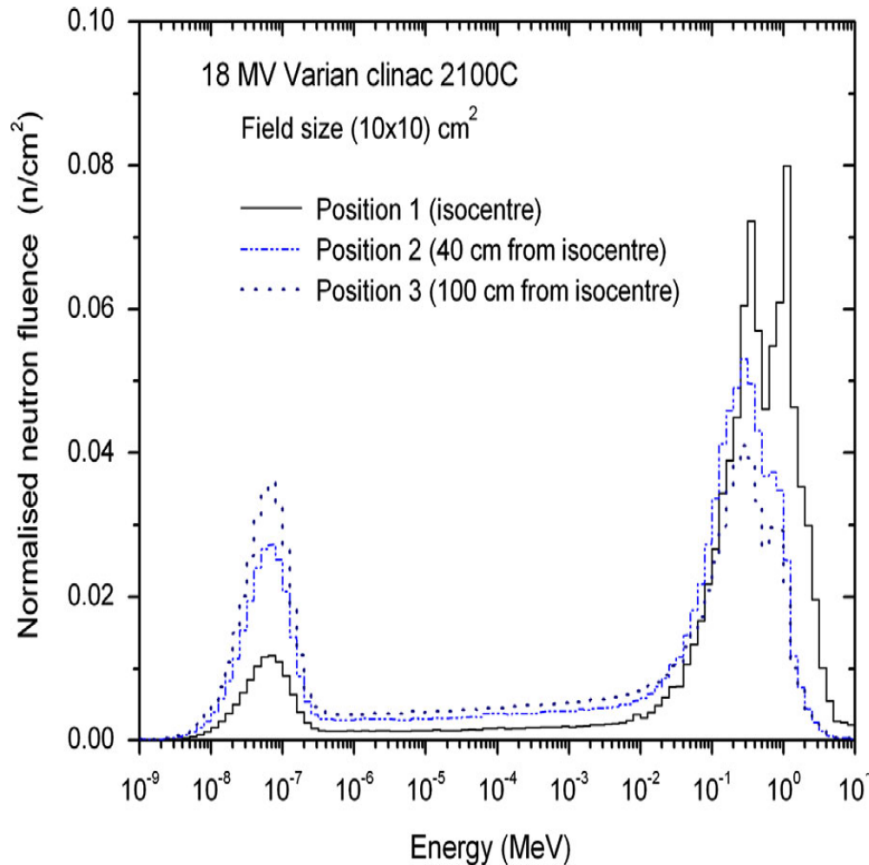


Figure 2: Photo-neutron Spectra at the Patient Couch, as measured using CR39 track detectors. [4, Alem]

Evaporation neutrons constitute the greatest part of the photo-neutrons and their spectra, as described by Tosi et al [5]:

$$\frac{dN}{dE_n} = \frac{E_n}{T^2} \exp\left(\frac{-E_n}{T}\right)$$

$$n(E) = A \frac{E}{T^2} \exp\left[-\frac{E}{T}\right] + B \frac{\ln\left[\frac{E_{max}}{E+S}\right]}{\int_0^{E_{max}-S} \ln\left[\frac{E_{max}}{E+S}\right] dE}$$

Evaporation  
neutrons

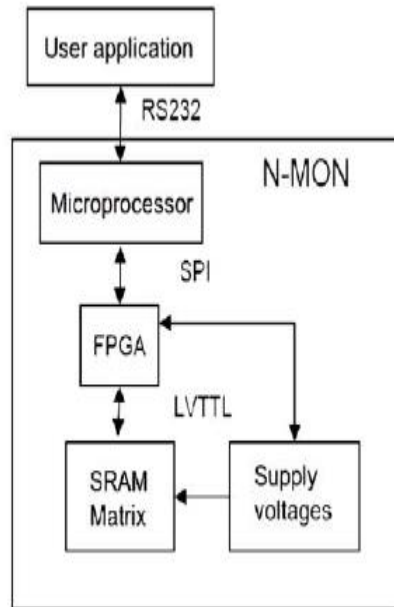
Fast  
neutrons

# Single Event Upset of Static random access memory (SRAM)

(SEU) in digital devices are produced by the ionization charge released from the interaction in silicon of particles like heavy ions, recoil nuclei or nuclear fragments from neutron interactions.



Figure 6: SRAM readout board. [Auerlio, 10]



SRAMs change the logical level of their cells when are exposed to neutrons.

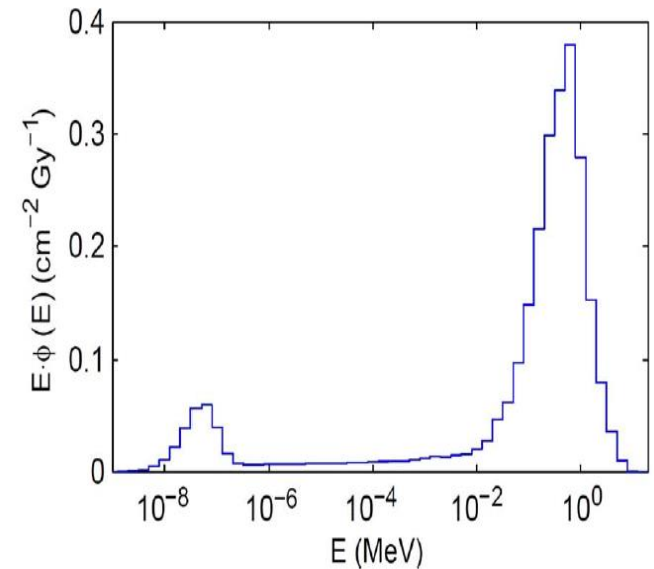
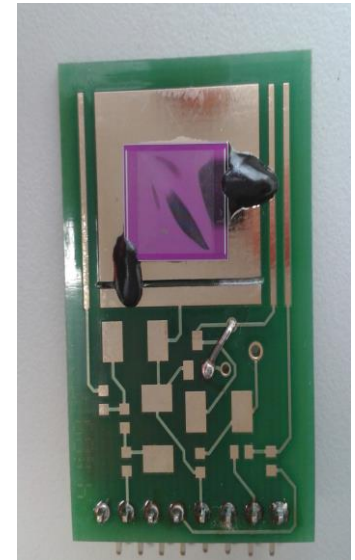
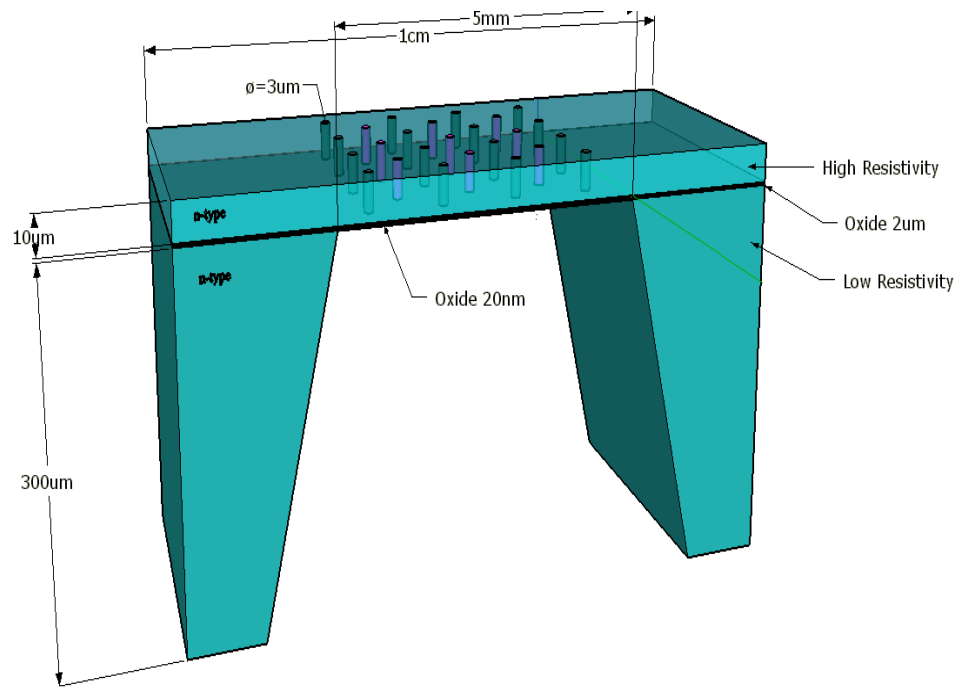


Figure 7: Neutron lethargy for a medical linac working at 15MV measured using SRAM device. Fluence normalized to 1 Gy photon

# 3D Thin Neutron Detector – 10 $\mu$ m



- CNM: Spanish Detector (8b)
- n-type silicon
- High gamma rejection
- Fast response

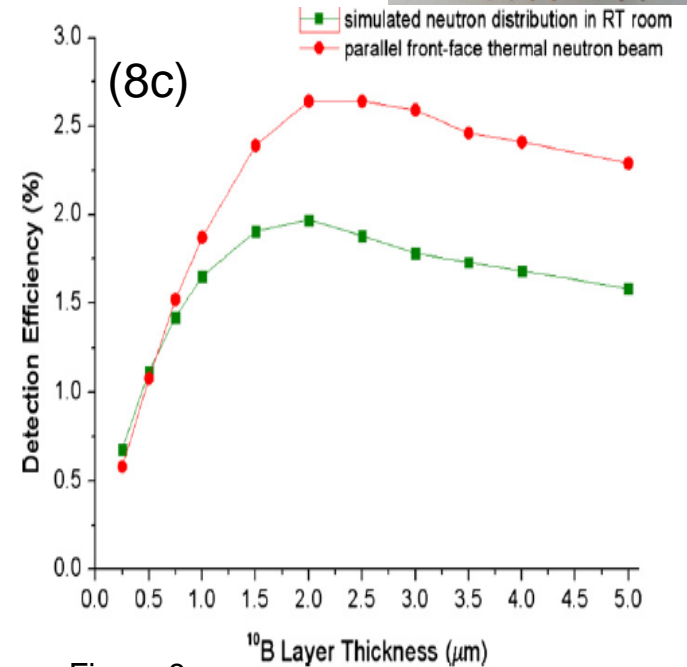
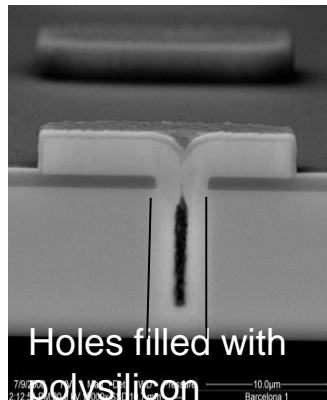
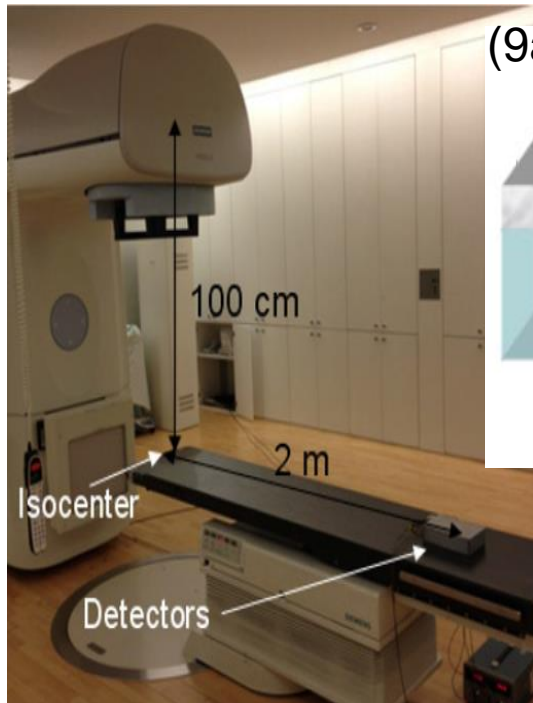
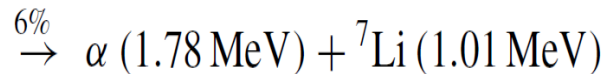
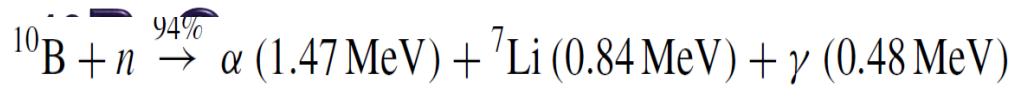


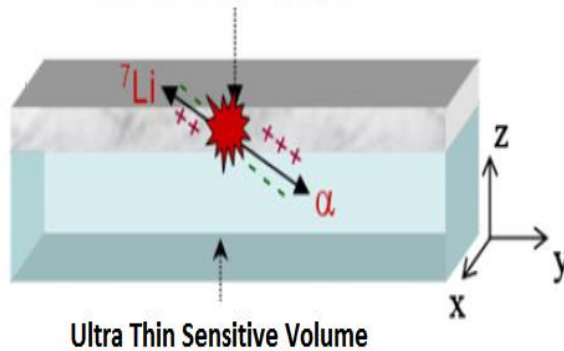
Figure 8c:

Figure 8a, 8b: 3D thin Neutron Detector Schematic.

# Neutron Measurements in RT Room with Ultra thin Detectors adapted with



(9a)  $^{10}\text{B}$  Based Converter Screen



- 10x10 Field Size
- 1000 MU at 500MU/min

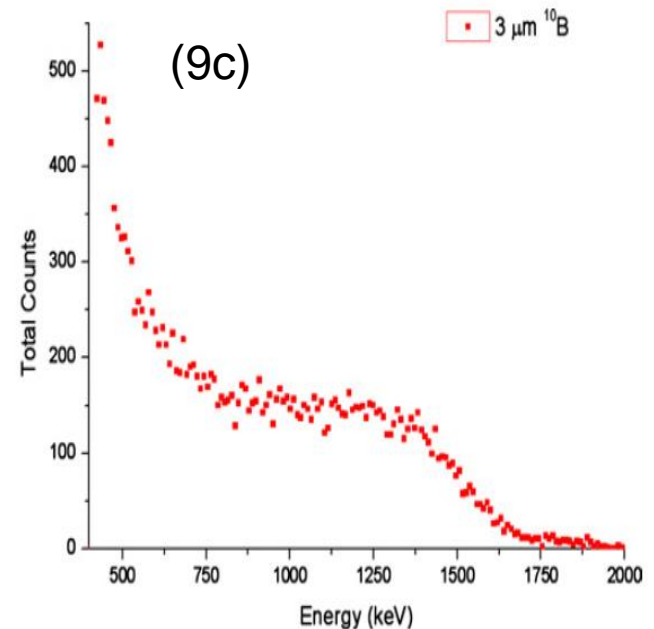
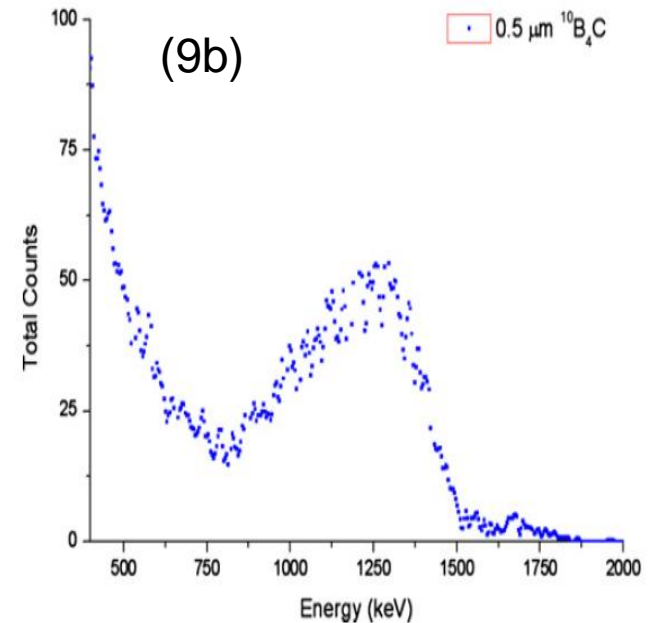


Figure 9a, 9b, 9c : 3D thin Neutron Detector Schematics.



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# MMND & ITRO 2016

Mini-Micro-Nano-Dosimetry and  
Innovative Technologies in Radiation Oncology Workshops



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